

AD-A046 480 HARRY DIAMOND LABS ADELPHI MD
IMPLEMENTATION OF THE DEVICE DATA BANK ON THE HDL IBM COMPUTER. (U)
OCT 77 T V NOON

UNCLASSIFIED

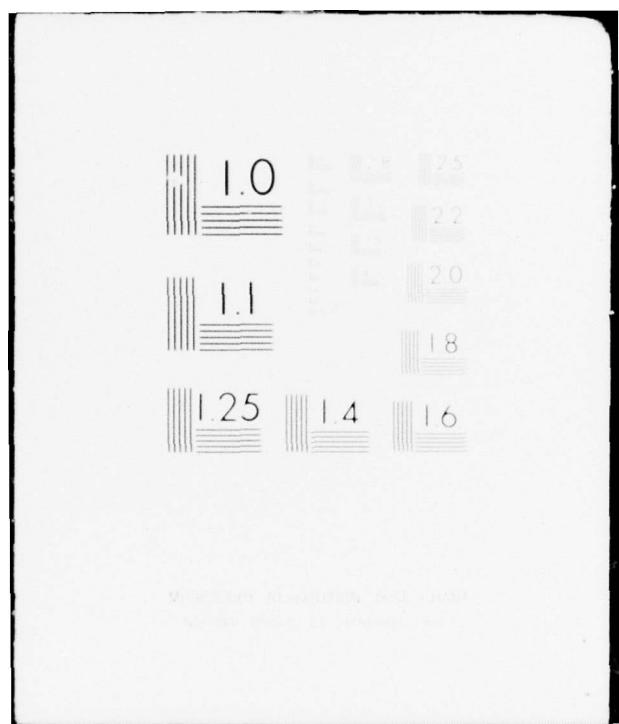
HDL-TR-1819

F/0 9/5

NL

| OF |
AO
AO46480





HDL-TR-1819

1
P2
B.S.

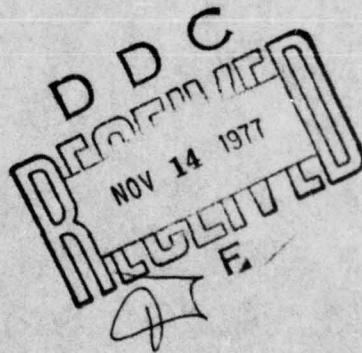
AD A046480

Implementation of the Device Data Bank
on the HDL IBM Computer

October 1977

TR-1819—*Implementation of the Device Data Bank on the HDL IBM Computer*, by Thomas V. Noon

AD NO.
DDC FILE COPY



U.S. Army Materiel Development
and Readiness Command
HARRY DIAMOND LABORATORIES
Adelphi, Maryland 20783

APPROVED FOR PUBLIC RELEASE; DISTRIBUTION UNLIMITED.

The findings in this report are not to be construed as an official Department of the Army position unless so designated by other authorized documents.

Citation of manufacturers' or trade names does not constitute an official indorsement or approval of the use thereof.

Destroy this report when it is no longer needed. Do not return it to the originator.

UNCLASSIFIED

SECURITY CLASSIFICATION OF THIS PAGE (When Data Entered)

REPORT DOCUMENTATION PAGE			READ INSTRUCTIONS BEFORE COMPLETING FORM
1. REPORT NUMBER HDL-TR-1819	2. GOVT ACCESSION NO.	3. RECIPIENT'S CATALOG NUMBER 9	
4. TITLE (and Subtitle) Implementation of the Device Data Bank on the HDL IBM Computer.		5. TYPE OF REPORT & PERIOD COVERED Technical Report	
6. PERFORMING ORG. REPORT NUMBER		7. CONTRACT OR GRANT NUMBER(s) DA: 1L162118AH75 PRON: A17R000402A1A9	
8. AUTHOR(s) Thomas V. Noon		9. PERFORMING ORGANIZATION NAME AND ADDRESS Harry Diamond Laboratories 2800 Powder Mill Road Adelphi, MD 20783 12 89 P.	
10. PROGRAM ELEMENT, PROJECT, TASK AREA & WORK UNIT NUMBERS Program Ele: 62118A		11. CONTROLLING OFFICE NAME AND ADDRESS U.S. Army Materiel Development and Readiness Command Alexandria, VA 22333 11	
12. REPORT DATE Oct 1977		13. NUMBER OF PAGES 93	
14. MONITORING AGENCY NAME & ADDRESS (if different from Controlling Office)		15. SECURITY CLASS. (of this report) Unclassified	
16. DISTRIBUTION STATEMENT (of this Report) Approved for public release; distribution unlimited.		15a. DECLASSIFICATION/DOWNGRADING SCHEDULE	
17. DISTRIBUTION STATEMENT (of the abstract entered in Block 20, if different from Report)			
18. SUPPLEMENTARY NOTES HDL Project: X757E2 DRCMS Code: 612118H750011 This work was sponsored by the Department of the Army under project 1W162118AH75/CA, Multiple Systems Evaluation Program.			
19. KEY WORDS (Continue on reverse side if necessary and identify by block number) Device Data Bank Semiconductor damage data Device library DAMTRAC Semiconductor devices			
20. ABSTRACT (Continue on reverse side if necessary and identify by block number) The Device Data Bank, as used by the DAMTRAC and, in the near future, the NET2 circuit-analysis programs on the Harry Diamond Laboratories' IBM 370/168 computer, is presented. The new file structure of the device libraries, access method for use of the device parameters by DAMTRAC and other computer programs, and a management program to manage and maintain the device data bank are presented in detail. The job control language (JCL) for executing the IBM version of DAMTRAC on the HDL computer is also presented.			

163 050

not

CONTENTS

	<u>Page</u>
1. INTRODUCTION	5
2. DESCRIPTION OF THE DEVICE DATA BANK FILES	7
2.1 Diode Device Library	7
2.2 Transistor Device Library	7
3. MANAGEMENT PROGRAM FOR THE DEVICE DATA BANK--MPD2B	10
3.1 Description of MPD2B	10
3.2 Description of the Action Requests	10
3.2.1 CREATE	10
3.2.2 UPDATE	11
3.2.3 ADD TO	11
3.2.4 LIST	11
3.2.5 END OF ACTION	11
3.2.6 FINISH	11
3.3 Device Data Entry Format	12
3.3.1 Diode Device Library	12
3.3.2 Transistor Device Library	13
3.4 Program Messages Issued by MPD2B	17
3.5 Sample Action Requests	18
4. INTERFACING DEVICE DATA BANK WITH DAMTRAC	19
5. LISTING OF DIODE AND TRANSISTOR DEVICE LIBRARIES	20
APPENDIX A.--JCL FOR EXECUTING DAMTRAC AT HDL	87
DISTRIBUTION	89

FIGURES

1 The GAMPHS application in vulnerability and hardness assessment	6
2 Simple diode data set	14
3 Sample transistor data set	16

ACCESSION for	
NTIS	W. C. Johnson
DDC	Buff Section
UNANNOUNCED	<input checked="" type="checkbox"/>
JUSTIFICATION	
BY	
DISTRIBUTION/AVAILABILITY CODES	
Dist	Avail
A	B3 G.P.

PRECEDING PAGE BLANK-NOT FILMED

TABLES

	<u>Page</u>
I Definition of Diode Equivalent-Circuit Values and Damage Values	8
II Definition of Transistor Equivalent-Circuit Values and Damage Values	9
III Device Parameter References	83

1. INTRODUCTION

The effects of high-altitude electromagnetic pulses (HEMP) from nuclear weapons deployed at high altitudes can seriously degrade tactical weapon and communication systems vitally needed by the field Army prepared to fight a conventional and nuclear war. The Multiple Systems Evaluation Program (MSEP) was established to determine both the vulnerability of and the means for hardening many of these Army tactical systems to an HEMP environment. An essential step in the program is to develop analytic tools (such as computer programs for predicting transient data and system response) to evaluate system susceptibility to HEMP. These computer programs have been gathered into an applications package titled Generic Assessment Methods for a Priori Hardening of Systems (GAMPHS).¹ The GAMPHS application for the vulnerability and hardness assessment of systems covered by MSEP uses the programs described in this report in addition to other computer programs (see fig. 1).

This report describes one aspect of the effort by the Harry Diamond Laboratories (HDL) to convert DAMTRAC² (Damage Analysis Modified Transient Radiation Analysis by Computer) and the Device Data Bank* (consisting of files of diodes and transistors with their equivalent-circuit parameters and damage data) from the Mobility Equipment Research and Development Command CDC computer to the HDL IBM 370/168 computer. The transmutations and modifications required to convert DAMTRAC are basically transparent to users of the CDC version of DAMTRAC except for the control language which directs the job execution (the job control language (JCL) for DAMTRAC is presented in app A). However, the conversion of the Device Data Bank files required the restructuring of the data files and the development of new programs to manage and maintain the data files, and to access and retrieve device data from these files. The file structure, management programs, and access method is discussed in detail in this report. Sufficient information about the software described in this report is provided to allow a programmer experienced in IBM FORTRAN and JCL and in the use of DAMTRAC to use the programs and concepts. Complete listings of the device libraries and parameter references are presented in section 5.

¹George Gornak et al, *EMP Assessment for Army Tactical Communications Systems: Transmission Systems, Series No. 1--Radio Terminal Set AN/TRC-145 (U)*, Harry Diamond Laboratories TR-1746 (February 1976). (SECRET RESTRICTED DATA) *C6032936*

²George Baker et al, *Damage Analysis Modified TRAC*, Harry Diamond Laboratories TM-76-6 (May 1975). *HDL-76-76*

*Charles P. Ruzic, *Extension and Interfacing the MSEP Semiconductor Damage Data Bank for Analysis and Retrieval by DAMTRAC*, Harry Diamond Laboratories TR-1821 (December 1977).

MULTIPLE SYSTEMS EVALUATION PROGRAM
COMPUTER PROGRAM FLOW IN VULNERABILITY ASSESSMENT

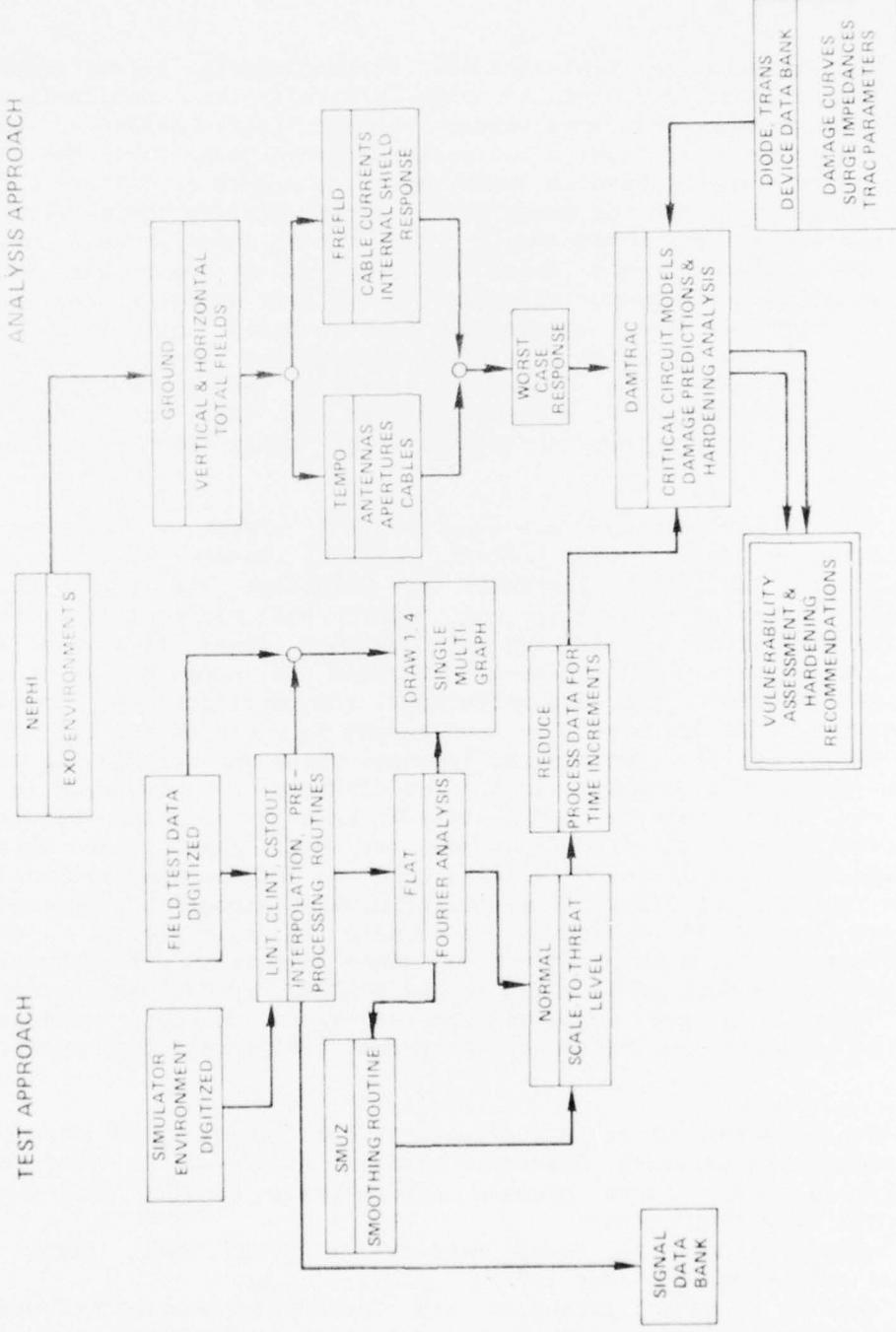


Figure 1. The GAMPHS application in vulnerability and hardness assessment.

2. DESCRIPTION OF THE DEVICE DATA BANK FILES

The Device Data Bank files are a collection of the equivalent-circuit values and damage parameters of different diode and transistor types stored by their device names. The equivalent-circuit and damage parameters are used as input for circuit analysis and for calculations of circuit damage due to EMP (electromagnetic pulse) by programs such as DAMTRAC and NET2. The existence of these files reduces the input data required by the circuit-analysis program by allowing the program users to specify only a device name. The circuit-analysis programs then search the Device Data Bank file for the device parameter.

The Device Data Bank files were created at HDL, using the IBM direct access file structure. The direct access file structure allows for access and modification of multirecord files at random without regard for the records' physical location. This random selection of records is a very desirable attribute for files of data which are retrieved by name keys (such as diode and transistor types).

2.1 Diode Device Library

The Diode Device Library is a direct access file with space reserved for 300 different diode types. Each diode type has space reserved for 19 device parameters, 11 parameter references, and a status flag. The 19 device parameters consist of the 7 TRAC³ equivalent-circuit values and 12 device-damage values (4 presently unused). The definition of the diode device parameters is given in table I (p 8). The parameter references (see sect. 5) refer to the origin of the TRAC values and the last 10 damage values. The status flag (titled TRAC FLAG on the listings of the device library) indicates whether the proper TRAC equivalent-circuit values are defined for use of the device library entry by the DAMTRAC circuit-analysis program. If the TRAC FLAG is set to 1, all the necessary device parameters have been defined; if the TRAC FLAG is set to 0, all the necessary device parameters have not been defined and therefore cannot be used as input for DAMTRAC runs.

2.2 Transistor Device Library

The Transistor Device Library is a direct access file with space reserved for 300 different transistor types. Each transistor type has space reserved for 40 device parameters, 10 parameter references, and a status flag. The 40 device parameters consist of the 16

³E. D. Johnson et al, *Transient Radiation Analysis by Computer Program (TRAC)*, Autonetics Division of North American Rockwell Corp., AD 836683 (June 1968).

TABLE I. DEFINITION OF DIODE EQUIVALENT-CIRCUIT VALUES AND DAMAGE VALUES

Note: P = power to damage; τ = pulse duration

Symbol	Definition
I_S	Reverse saturation current*
M_D	Proportionality constant*
R_{DL}	Leakage resistance*
C_{DO}	Junction capacitance constant*
V_{DBI}	Diffusion or built-in voltage*
T_D	Diode time constant*
I_{PPD}	Primary photocurrent constant*
V_B	Breakdown voltage*
Surge Z	Reverse surge impedance*
R Bulk Forward	Forward bulk resistance
Surge Z Rev 1 μ s	Reverse surge impedance for 1- μ s square pulse
Surge Z Rev 10 μ s	Reverse surge impedance for 10- μ s square pulse
K Damage Rev <50 ns	Measured reverse damage constant ($\tau < 50$ ns) $K = P\tau$
K Damage Rev >50 ns	Measured reverse damage constant ($\tau > 50$ ns) $K = P\tau^{\frac{1}{2}}$
K Damage Forward	Measured forward damage constant using $K = P\tau$
K	Not used, available of other damage constants

*Used by DAMTRAC for diode model.

TRAC³ equivalent-circuit values and 24 device-damage values (6 presently unused). The definitions of the transistor device parameters are given in table II. The parameter references (see sect. 5) refer to the origin of the last 20 damage values. The status flag (titled TRAC FLAG on the listings of the device library) indicates whether the proper TRAC equivalent-circuit values are defined for use of the device library entry by the DAMTRAC circuit-analysis program. If the TRAC FLAG is set to 1, all the necessary device parameters have been defined; if the TRAC FLAG is set to 0, all the necessary device parameters have not been defined and therefore cannot be used as input for DAMTRAC runs.

³E. D. Johnson et al, *Transient Radiation Analysis by Computer Program (TRAC)*, Autonetics Division of North American Rockwell Corp., AD 836683 (June 1968).

TABLE II. DEFINITION OF TRANSISTOR EQUIVALENT-CIRCUIT VALUES AND DAMAGE VALUES.

Note: P = power to damage; τ = pulse duration

Symbol	Definition
HFEN	Normal common-emitter current gain*
HFEI	Inverse common-emitter current gain*
TN	Emitter-time constant*
TI	Collector-time constant*
ICS	Collector reverse-saturation current*
MC	C-B proportionality constant in exponent*
CCO	C-B junction capacitance at zero bias*
VCBI	C-B junction-diffusion potential*
RCL	C-B leakage resistance*
IES	Emitter reverse-saturation current*
ME	E-B proportionality constant in exponent*
CEO	E-B junction capacitance at zero bias*
VEBI	E-B junction diffusion potential*
REL	E-B leakage resistance*
IPPC	Primary photocurrent for the collector-base junction*
IPPE	Primary photocurrent for the emitter-base junction*
C-BBDV	C-B breakdown voltage*
E-BBDV	E-B breakdown voltage*
Surge ZC	C-B reverse surge impedance (0.1- μ s pulse width)*
Surge ZE	E-B reverse surge impedance (0.1- μ s pulse width)*
Bulk Resistance C-B	Junction forward bulk resistance
Bulk Resistance E-B	Junction forward bulk resistance
Z Surge C-B 1 μ s	Reverse surge impedance (1- μ s pulse width)
Z Surge C-B 10 μ s	Reverse surge impedance (10- μ s pulse width)
Z Surge E-B 1 μ s	Reverse surge impedance (1- μ s pulse width)
Z Surge E-B 10 μ s	Reverse surge impedance (10- μ s pulse width)
Damage K (<50 ns)C-B	Reverse biased damage constant ($t < 50$ ns) $K = P\tau$
Damage K (<50 ns)E-B	Reverse biased damage constant ($t < 50$ ns) $K = P\tau$
Damage K (>50 ns)C-B	Reverse biased damage constant ($t > 50$ ns) $K = P^{\frac{1}{2}}\tau$
Damage K (>50 ns)E-B	Reverse biased damage constant ($t > 50$ ns) $K = P^{\frac{1}{2}}\tau$
K Forward C-B	Forward biased damage constant $K = P\tau$
K Forward E-B	Forward biased damage constant $K = P\tau$
K	Available for other damage constants

*Used by DAMTRAC for transistor model.

3. MANAGEMENT PROGRAM FOR THE DEVICE DATA BANK--MPD2B

3.1 Description of MPD2B

To simplify and minimize the effort necessary to manage and maintain the Device Data Bank, only one program, MPD2B, is required to create, update, add to, and list the device libraries. Through the use of action requests and action control cards as part of the required input data to the program, any of the above-mentioned functions can be performed on either or both device libraries in one job. Each action request specifies the action to be taken and the library to which the action refers. The action requests for the device libraries are as follows.

For the Diode Device Library:

- (1) CREATE DIODE FILE
- (2) UPDATE DIODE FILE
- (3) ADD TO DIODE FILE
- (4) LIST DIODE FILE

For the Transistor Device Library:

- (1) CREATE TRANSISTOR FILE
- (2) UPDATE TRANSISTOR FILE
- (3) ADD TO TRANSISTOR FILE
- (4) LIST TRANSISTOR FILE

The action control cards, END OF ACTION and FINISH, are required to terminate one action request (CREATE, UPDATE, ADD TO) and either prompt the program for another action request or signal the end of the job. For all action requests and action control cards, the command (CREATE, UPDATE, ADD TO, LIST, END OF ACTION, FINISH) must begin in column 1 of the data card, and for action requests specifying a file name (CREATE, UPDATE, ADD TO, LIST), the file name (DIODE FILE, TRANSISTOR FILE) must begin in column 8 of the data card. Improper coding of an action request or action control card causes the job to stop with a user-supplied STOP code of 1.

3.2 Description of the Action Requests

3.2.1 CREATE

The action request CREATE must be the first action request for either device library. The CREATE action request establishes the file definition requirements and writes the supplied device data onto the file beginning at the second record and continuing onto subsequent records for each different device name until an END OF ACTION control card is encountered. After the END OF ACTION control card is read, the record index and the date of the creation run are written onto the first record for use by the LIST action requests.

3.2.2 UPDATE

The UPDATE action request is used for changing parameter values previously defined or for defining new parameter values for devices already in the pertinent device library. Device data are read and the appropriate device record updated until an END OF ACTION control card is encountered. An UPDATE flag and the date of the update run are then written onto the first record for use by the LIST action request to indicate the last action performed on the device library.

3.2.3 ADD TO

The ADD TO action request is used for adding new device entries to a device library. Device data are read with each new device added to the next available record in the file until an END OF ACTION control card is encountered. After the END OF ACTION control card is read, the new record index, an ADD TO flag, and the date of the add run are written onto the first record for use by the LIST action request to indicate the last action performed on the device library.

3.2.4 LIST

The LIST action request is used for listing the devices, device parameters, parameter references, and TRAC flag that are stored in a device library. Each device name is listed along with its associated parameter values. The devices are listed in the IBM collating sequence starting with the first character of the device name. In addition to the list of devices, a title page is printed giving the name of the device library (i.e., Diode Device Library, Transistor Device Library), the current date, the library creation date, and the last action request of the file (if any) and its date. The words "End of Listing" are printed after the last device to signify the end of the listing. The LIST action request should be the last action taken on a file after every run of the MPD2B program. Also, the LIST action request does not need to be followed by an END OF ACTION action request as the LIST action request does not read any data from the input stream.

3.2.5 END OF ACTION

The END OF ACTION action control card is used to terminate the input data to an action request (CREATE, UPDATE, ADD TO). An END OF ACTION card must follow the input data for all the previous action requests. An END OF ACTION card is not required after the LIST action request since there are no input data to this command.

3.2.6 FINISH

The FINISH action control card terminates the input data for the MPD2B program. The FINISH action control card must be the last card of the input data.

3.3 Device Data Entry Format

3.3.1 Diode Device Library

To enter diode device data into the Diode Device Library, four data cards are required for each different device. Each data card contains the device name in columns 1 through 12, with the name left justified; the remainder of each card contains the appropriate values for the parameters and parameter references according to the following order (see table I, sect. 2 for definitions of parameters) and formats:

Card 1: Device Name, IS,
MD,
RDL,
CDO,
VDBI,
TD

Card 2: Device Name, IPPD,
VB,
Surge Z,
R Bulk Forward,
Surge Z Rev 1 μ s,
Surge Z Rev 10 μ s

Card 3: Device Name, K Damage Rev <50 ns,
K Damage Rev >50 ns,
K Damage Forward,
K,
K,
K

Card 4: Device Name, K,
TRAC Ref,
R Bulk Forward Ref,
Surge Z Rev 1 μ s Ref,
Surge Z Rev 10 μ s Ref,
K Damage Rev <50 ns Ref,
K Damage Rev >50 ns Ref,
K Damage Forward Ref,
K Ref,
K Ref,
K Ref,
K Ref

Format for Cards 1, 2, and 3: (3A4, 3X, 6E10.3)
Format for Card 4: (3A4, 3X, E10.3, 6X 11
(1X, I3))

Sample diode data set: (see fig. 2, p 14)

Diode type 1N1202	
IS = 4.25×10^{-10}	Surge Z = 64
MD = 1.62	R Bulk Forward = 1, Ref No. 25
RDL = 4.13×10^{10}	Surge Z Rev 1 μs = 65, Ref No. 25
CDO = 1.3×10^{-11}	Surge Z Rev 10 μs = 65, Ref No. 25
VDBI = 1	K Damage Rev <50 ns = not defined
TD = 1×10^{-7}	K Damage Rev >50 ns = 14, Ref No. 25
IPPD = 1×10^{-4}	K Damage Forward = not defined
VB = 200	TRAC Ref = not defined

For UPDATE action requests, all four data cards for the device being updated must be used as input. All parameter values and parameter reference values which were previously defined must be present on the data cards because the entire record is updated from the input data cards. The reason for this requirement is to make the maintenance of a hard copy of the device library less of a chore for the Device Data Bank manager.

3.3.2 Transistor Device Library

To enter transistor device data into the Transistor Device Library, seven data cards are required for each different device. Each data card contains the device name in columns 1 through 12, with the name left justified; the remainder of each card contains the appropriate values for the parameters and parameter references according to the following order (see table II, sect. 2 for definition of parameters) and formats.

Card 1: Device Name, HFEN,
HFEI,
TN,
TI,
ICS,
MC
Card 2: Device Name, CCO,
VCBI,
RCL,
IES,
ME,
CEO
Card 3: Device Name, VEBI,
REL,
IPPC,
IPPE,
C-BBDV,
E-BBDV

Figure 2. Sample diode data set.

Card 4: Device Name, Surge ZC,
 Surge ZE,
 Bulk Resistance C-B,
 Bulk Resistance E-B,
 Z Surge C-B 1 μ s,
 Z Surge C-B 10 μ s
 Card 5: Device Name, Z Surge E-B 1 μ s,
 Z Surge E-B 10 μ s,
 Damage F (<50 ns) C-B,
 Damage K (<50 ns) E-B,
 Damage K (>50 ns) C-B,
 Damage K (>50 ns) E-B
 Card 6: Device Name, K Forward C-B,
 K Forward E-B,
 K C-B,
 K E-B,
 K C-B,
 K E-B,
 Card 7: Device Name, Bulk Resistance Ref,
 Z Surge C-B Ref,
 Z Surge E-B Ref,
 Damage K (<50 ns) Ref,
 Damage K (>50 ns) Ref,
 K Forward Ref,
 K Ref,
 K Ref

Format for Cards 1, 2, 3, 4, 5, and 6: (3A4, 3X, 6E10.3)
 Format for Card 7: (3A4, 10(1X, I3))

Sample transistor data set: (see fig. 3)

Transistor type 2N705

HFEN = 25	C-BBDV	= 15	
HFEI = not defined	E-BBDV	= 3.5	
TN = 1.06×10^{-9}	Surge ZC	= 72.5	
TI = 5.03×10^{-8}	Surge ZE	= 165	
ICS = 10^{-5}	Bulk Resistance C-B	= 0.95	Ref No. 34
MC = 1.83	Bulk Resistance E-B	= 2.2	
CCO = 1.37×10^{-11}	Z Surge C-B 1 μ s	= 150	Ref No. 34
VCBI = 0.3	Z Surge C-B 10 μ s	= 360	
RCL = 10^7	Z Surge E-B 1 μ s	= 340	Ref No. 34
IES = 10^{-5}	Z Surge E-B 10 μ s	= 340	
ME = 1.83	Damage K (<50 ns) C-B	= 3.18×10^{-6}	Ref
CEO = 6.39×10^{-12}	Damage K (<50 ns) E-B	= 1.13×10^{-6}	No. 60
VEBI = 0.3	Damage K (>50 ns) C-B	= 1.42×10^{-2}	
REL = 10^7	Damage K (>50 ns) E-B	= 5.06×10^{-3}	No. 60
IPPC = 10^{-3}	K Forward C-B	= 7.9×10^{-5}	Ref
IPPE = 10^{-5}	K Forward E-B	= 3.6×10^{-5}	No. 60

STN. NO.	1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28 29 30 31 32 33 34 35 36 37 38 39 40 41 42 43 44 45 46 47 48 49 50 51 52 53 54 55 56 57 58 59 60 61 62 63 64 66 67 68 69 70 71 72 73 74 75 76 77 78 79 80
2N705	• 2.50E+02
2N705	• 3.7E+11Q
2N705	• 3.00E+00
2N705	• 3.00E+08
2N705	• 1.00E+02
2N705	• 7.25E+02
2N705	• 3.40E+03
2N705	• 34

Figure 3. Sample transistor data set.

For UPDATE action requests, all seven data cards for the device being updated must be used as input. All parameter values and parameter reference values which were previously defined must be present on the data cards because the entire record is updated from the input data cards. The reason for this requirement is to make the maintenance of a hard copy of the device library less of a chore for the Device Data Bank manager.

3.4 Program Messages Issued by MPD2B

The following messages are printed during the execution of the MPD2B program.

*****ERROR ON INPUT CONTROL CARD
*****JOB TERMINATED

This message is printed when an action request card is not recognized. The job is terminated. This message is accompanied by a STOP 1.

*****DATA FOR X DEVICES SUCCESSFULLY WRITTEN ON DEVICE SET Y

This message is printed at the completion of a successful CREATE run. Here, X is the number of devices written on the file and Y is the device set where the data were written (11 for the diode file and 12 for the transistor file).

*****UPDATING OF THE DIODE FILE COMPLETED
or
*****UPDATING OF THE TRANSISTOR FILE COMPLETED

These messages are printed at the completion of a successful UPDATE run.

*****DEVICES SUCCESSFULLY ADDED TO DIODE FILE
or
*****DEVICES SUCCESSFULLY ADDED TO TRANSISTOR FILE

This message is printed at the completion of a successful ADD TO run.

*****END ENCOUNTERED UNEXPECTEDLY ON INPUT

This message is printed if an end of record card is read during the input of data. This message is accompanied by a STOP 1.

*****DEVICES NAMES DO NOT MATCH FOR DEVICE X (Y)

This message is printed if the device names do not match while the input data cards for a particular device are read. Here, X is the device name first read and Y is the device name read which did not match. This message is accompanied by a STOP 1.

*****DEVICE NAME NOT LOCATED IN DIODE FILE
or

*****DEVICE NAME NOT LOCATED IN TRANSISTOR FILE

These messages are printed during an UPDATE run if the device to be updated is not located in the file. This message is accompanied by a STOP 3.

*****DEVICE X IS ALREADY IN THE DIODE DEVICE DATA FILE
(ITEM No. Y)

or

*****DEVICE X IS ALREADY IN THE TRANSISTOR DEVICE DATA FILE
(ITEM No. Y)

These messages are printed during an ADD TO run if device X, to be added to the file, is already in the device file. The item Y is the location of the device on a current listing of the file.

*****INDEXING ERROR WHILE UPDATING DIODE DEVICE DATA FILE

*****INDEXING ERROR WHILE UPDATING TRANSISTOR DEVICE DATA FILE

*****INDEXING ERROR WHILE ADDING TO DIODE DEVICE DATA FILE

*****INDEXING ERROR WHILE ADDING TO TRANSISTOR DEVICE DATA FILE

*****INDEXING ERROR WHILE LISTING DIODE DEVICE DATA FILE

or

*****INDEXING ERROR WHILE LISTING TRANSISTOR DEVICE DATA FILE

These messages are printed if the indexing key stored with the file has been corrupted. The indexing key is checked for the UPDATE, ADD TO, and LIST action requests. A CREATE run for the particular file is recommended. This message is accompanied by a STOP 2.

*****END OF JOB

This message is printed after the FINISH action request has been processed.

3.5 Sample Action Requests

The following are sample action request input data for MPD2B. The last action request to any device file for any run should be the LIST action request.

Sample action request input for a CREATE run
CREATE DIODE FILE
(enter diode device data)
END OF ACTION
LIST DIODE FILE
FINISH

Sample action request input for an UPDATE and ADD TO run
UPDATE DIODE FILE
(enter diode device data)
END OF ACTION
ADD TO TRANSISTOR FILE
(enter transistor device data)
END OF ACTION
LIST DIODE FILE
LIST TRANSISTOR FILE
FINISH

It should be noted that the action requests to the diode or transistor data files can be used in any order and do not have to be grouped by file types.

4. INTERFACING DEVICE DATA BANK WITH DAMTRAC

The interfacing of the IBM versions of the Device Data Bank and DAMTRAC was accomplished in much the same manner as was used in the CDC versions. Circuit piece-part data decks constructed for use with the MERADCOM CDC version of DAMTRAC require no changes to be used as input for the HDL IBM version. The manner of requesting the device parameter to be read from the Device Data Bank has remained the same; "device name/R" states that the device parameters do not follow but must be read from the appropriate device library. Only the supporting subroutine which retrieves the appropriate device parameter is different.

The subroutine OPENDA with entry points READD A and WRITDA was written to provide DAMTRAC with the proper access method to the Device Data Bank. Subroutine OPENDA contains the DEFINE FILE statements for the Diode and Transistor Device Libraries and the CALL to OPENDA fills and orders a table of device names for both device libraries. The CALL to READD A locates the device in the appropriate device table for which the parameters have been requested, and reads the requested device parameter into a DAMTRAC supplied array. Before returning to DAMTRAC, the TRAC FLAG for the device is checked. If all the necessary device parameters for the DAMTRAC analysis calculation are not defined (TRAC FLAG set to 0) a message is written on the line printer to notify the user of that fact and the job is terminated. However, if all the necessary device parameters are defined (TRAC FLAG set to 1) the device

parameters are returned to DAMTRAC. To maintain the integrity of the device libraries, the ability to enter device parameters into the device libraries from DAMTRAC was not implemented on the IBM version; however, to maintain compatibility with the DAMTRAC and TRAC manuals, a CALL to WRITDA is executed when a request to enter device parameters is encountered. The CALL to WRITDA writes a message on the line printer notifying the user that data cannot be written in a device library and then returns to DAMTRAC.

5. LISTING OF DIODE AND TRANSISTOR DEVICE LIBRARIES

To aid the EMP damage analyst, this section presents listings of the devices contained in the device libraries. Table III of the section gives parameter references found in the diode device library--for example, code 034 of table III is shown in the library as (34).

DIODE DEVICE LIBRARY

DIODE DEVICE LIBRARY (Cont'd)

DIODE DEVICE LIBRARY (Cont'd)

DEVICE NAME	I _D	V _D	K _D	K _{DL}	C _{DD}	V _{OBI}	T ₀	I _{PPO}	V _E	SURGE Z	TRAC REF
(TRAC FLAG) ^a	4.52E-10	1.62E+00	4.13E+10	1.30E-11	1.00E+00	1.00E-07	1.00E-04	4.00E+02	1.10E-01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0
(BULK) ^a	4.6E-14	1.06E+00	1.70E+10	2.60E-10	8.50E-01	2.15E-07	1.00E-04	8.75E+00	2.10E+01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0
(REV LUS) ^a	4.26E-14	1.03E+00	1.28E+10	4.12E-10	8.50E-01	1.94E-07	1.00E-04	8.75E+00	2.10E+01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0
(REV LUS) ^a	4.09E-14	1.02E+00	2.53E+10	2.49E-10	8.50E-01	2.61E-07	1.00E-04	8.75E+00	2.10E+01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0
(REV >20NS) ^a	1.05E-14	1.01E+00	1.96E+10	2.91E-10	8.00E-01	2.30E-07	1.00E-04	8.75E+00	2.10E+01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0
(FORWARD) ^a	1.00E-13	1.01E+00	1.50E+10	2.49E-10	8.00E-01	2.57E-07	1.00E-04	8.75E+00	2.10E+01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0
(REF) ^a	7.08E-14	1.08E+00	2.50E+10	4.02E-10	8.00E-01	2.49E-07	1.00E-04	8.75E+00	2.10E+01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0
(REF) ^a	5.00E-13	1.07E+00	8.00E+09	4.02E-10	8.00E-01	2.17E-07	1.00E-04	8.75E+00	2.10E+01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0
(REF) ^a	7.08E-14	1.08E+00	2.50E+10	4.02E-10	9.00E-01	2.17E-07	1.00E-04	1.28E+01	2.10E+01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0
(REF) ^a	5.00E-13	1.07E+00	8.00E+09	4.02E-10	9.00E-01	2.17E-07	1.00E-04	1.28E+01	2.10E+01	-----	-----
(1)	0	0	0	0	0	0	0	0	0	0	0

DIODE DEVICE LIBRARY (Cont'd)

PAGE 5

DEVICE NAME	M0	KDL	VDDI	TD	IPOD	VB	SURGE Z	(TRAC REF)
(KAC FLAG)	*	*	*	*	*	*	*	*
K-EOL	SURGE 2	SURGE 2	K DAMAGE	K FORWARD	K	K	K	K
FURSAU	REVIOUS	REVIOUS	REV >SONS	REV >SONS	REF	REF	REF	REF
(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)
IN1315B	3.30E-13	1.12E+00	2.60E+10	2.11E-10	9.00E-01	1.15E-07	1.00E-04	1.28E+01
(1)	+	+	+	+	+	+	+	+
IN1315C	6.60E-14	1.11E+00	1.40E+09	4.01E-10	9.00E-01	2.63E-07	1.00E-04	1.28E+01
(1)	+	+	+	+	+	+	+	+
IN1315C	4.36E-13	1.14E+00	7.00E+09	2.42E-10	9.00E-01	1.29E-07	1.00E-04	1.28E+01
(1)	+	+	+	+	+	+	+	+
IN1315F	7.25E-14	1.06E+00	2.50E+10	2.11E-10	9.00E-01	1.59E-07	1.00E-04	1.28E+01
(1)	+	+	+	+	+	+	+	+
IN140	2.67E-12	6.90E-01	1.60E+05	2.83E-11	5.00E-01	1.59E-07	1.00E-04	8.00E+01
(1)	+	+	+	+	+	+	+	+
IN14E2	1.00E-13	1.00E+00	1.00E+07	1.00E-09	1.00E+00	1.00E-12	1.00E-04	4.70E+00
(1)	+	+	+	+	+	+	+	+
IN1614	9.42E-12	1.30E+00	2.40E+11	4.00E-12	8.50E-01	1.00E-07	1.00E-04	2.00E+02
(1)	+	+	+	+	+	+	+	+
IN1731A	0	0	0	0	0	0	0	1.45E+03
(1)	0	0	0	0	0	0	0	0

DIODE DEVICE LIBRARY (Cont'd)

245

DIODE DEVICE LIBRARY (Cont'd)

PAGE 7

DEVICE NAME	1.5	8D	RDL	CDO	VDBI	ID	IPOD	VB	SURFACE	SURFACE
(TRAC FLAG)	*	*	*	*	*	*	*	*	K	REF
1N273E	3.51E-06	1.72E+00	4.50E+06	7.82E-13	5.50E-01	5.78E-09	1.00E-04	3.20E+01	2.10E+01	*
(1)	*	*	*	*	*	*	*	*	*	*
1N273F	2.82E-06	1.24E+00	1.60E+06	9.33E-13	5.00E-01	6.65E-09	1.00E-04	3.20E+01	2.10E+01	*
(1)	*	*	*	*	*	*	*	*	*	*
1N276	5.60E-07	1.94E+00	8.00E+05	5.00E-13	6.00E-01	6.50E-09	1.00E-04	1.00E+02	2.10E+01	*
(1)	*	*	*	*	*	*	*	*	*	*
1N277	9.44E-12	1.30E+00	2.40E+11	4.00E-12	8.50E-01	1.00E-07	1.00E-04	1.25E+02	5.10E+03	(61)
(1)	*	*	*	*	*	*	*	*	*	*
1N279	1.24E-06	1.67E+00	3.80E+06	2.83E-11	5.00E-01	3.18E-08	1.00E-04	3.20E+02	2.10E+02	*
(1)	*	*	*	*	*	*	*	*	*	*
1N2823E	4.52E-10	1.62E+00	4.13E+10	1.30E-11	1.00E+00	1.00E-07	1.00E-04	3.00E+01	2.10E+01	*
(1)	*	*	*	*	*	*	*	*	*	*
1N2846E	1.58E-09	1.68E+00	1.54E+09	1.22E-12	9.20E-01	1.00E-07	1.00E-04	2.00E+02	2.10E+01	*
(1)	*	*	*	*	*	*	*	*	*	*
1N291E	0	0	0	0	0	0	0	0	0	*
(1)	1.05E-01	5.50E-01	3.60E-01	7.08E-03	3.16E+01	1.50E+01	1.50E+01	0	1.50E+01	*
(1)	6.2	{ 34 }	{ 34 }	{ 60 }	{ 60 }	{ 17 }	{ 17 }	0	{ 17 }	*

DIODE DEVICE LIBRARY (Cont'd)

PAGE 8

DEVICE NAME	IS	MD	RDL	C00	V081	TD	I PPD	VB	SURGE Z	• (TRAC REF)
(TRAC FLAG)	+	-	-	-	-	-	-	-	-	-
R BULK	+	SURGE Z	SURGE Z	K DAMAGE	K DAMAGE	K DAMAGE	K	K	K	K
FORWARD	+	REV IUS	REV IUS	REVSONS	REVSONS	FORWARD	K	K	K	K
(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)

IN3024	1.39E-13	1.12E+00	1.00E+18	1.00E-18	9.00E-01	1.00E-07	1.00E-04	1.30E+01	2.10E+01	
(1)	0	0	0	0	0	0	0	0	0	0
IN3025E	1.39E-13	1.12E+00	1.00E+18	1.00E-18	9.00E-01	1.00E-07	1.00E-04	1.60E+01	3.50E+01	(61)
(1)	8.50E-02	3.50E-01	6.00E-01	8.49E-04	3.80E+00	4.40E-02	1.90E+00	0	0	0
	(34)	(62)	(62)	(60)	(60)	(60)	(17)	0	0	0
IN3027E	1.58E-09	1.68E+00	1.54E+09	1.20E-12	9.00E-01	1.00E-07	1.00E-04	2.00E+01	2.10E+01	
(1)	0	0	0	0	0	0	0	0	0	0
IN3031E	1.58E-09	1.68E+00	1.54E+09	1.20E-12	9.00E-01	1.00E-07	1.00E-04	3.60E+01	2.10E+01	
(1)	0	0	0	0	0	0	0	0	0	0
IN3034E	1.58E-09	1.68E+00	1.54E+09	1.20E-12	9.00E-01	1.00E-07	1.00E-04	3.90E+01	2.10E+01	
(1)	0	0	0	0	0	0	0	0	0	0
IN3066	9.10E-09	1.94E+00	4.50E+09	1.20E-12	9.00E-01	4.00E-09	1.00E-04	7.50E+01	5.00E+00	
(1)	0	0	0	0	0	0	0	0	0	0
IN3071	9.10E-09	1.94E+00	4.50E+09	1.50E-12	1.00E+00	8.00E-07	1.00E-04	2.00E+02	2.10E+01	
(1)	0	0	0	0	0	0	0	0	0	0
IN338	4.52E-10	1.62E+00	4.13E+10	1.30E-11	1.00E+00	1.00E-07	1.00E-04	1.00E-02	2.10E+01	
(1)	0	0	0	0	0	0	0	0	0	0

DIODE DEVICE LIBRARY (Cont'd)

PAGE 9

DEVICE NAME	REV	MD	KDL	CDC	VDD1	TO	IPPD	VB	SURGE Z	(TRAC REF)
(TAKA FLAG)	0	BULK	SURGE Z	K DAMAGE	K DAMAGE	K FORWARD	K	K	K	K
(TAKA FLAG)	0	FURAFU	KENIUS	REV 101	REV 201	REV 201	K	K	K	K
(KEF)	0	(KEF)	(KEF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)
1N3565	0	9.42E-12	1.30E+00	2.40E+11	4.00E-12	8.50E-01	1.00E-04	2.60E+01	2.00E+01	-----
(11)	0	0	0	0	0	0	0	0	0	0
1N3600	0	1.58E-09	1.66E+00	1.54E+09	1.20E-12	9.00E-01	1.00E-07	1.00E-04	5.00E+01	5.00E+00
(11)	0	3.57E-01	1.70E+01	1.30E+09	1.60E-01	1.90E-01	3.04E-04	0	0	0
(11)	0	(64)	(65)	(3)	(3)	(13)	(13)	(13)	(13)	0
1N3605	0	3.77E-09	1.26E+00	4.86E+09	6.57E-13	1.26E+00	5.79E-09	1.00E-04	4.00E+01	2.10E+01
(11)	0	0	0	0	0	0	0	0	0	0
1N3611	0	4.57E-10	1.62E+00	4.13E+10	1.30E-11	1.00E+00	1.00E-07	1.00E-04	2.00E+02	2.10E+01
(11)	0	0	0	0	0	0	0	0	0	0
1N3669	0	1.30E-10	1.28E+00	1.10E+06	2.30E-11	8.00E-01	4.64E-07	1.00E-04	7.00E+01	2.10E+01
(11)	0	0	0	0	0	0	0	0	0	0
1N4001	0	5.00E-09	1.84E+00	6.40E+08	1.30E-11	1.00E+00	1.19E-06	1.00E-04	5.00E+01	2.10E+01
(11)	0	0	0	0	0	0	0	0	0	0
1N4003	0	4.27E-09	1.76E+00	2.00E+10	2.30E-11	1.00E+00	6.82E-06	1.00E-04	1.50E+03	1.60E+02
(11)	0	0	0	0	0	0	0	0	0	0
1N4005	0	6.22E-09	1.84E+00	1.20E+09	3.60E-11	1.00E+00	1.48E-05	1.00E-04	1.50E+03	1.22E+02
(11)	0	0	0	0	0	0	0	0	0	0

DIODE DEVICE LIBRARY (Cont'd)

PAGE 10

DEVICE NAME	15	MD	ROL	CDO	VORI	TO	IPOD	VB	SURGE Z	(TRAC REF)
(TRAC FLAG)	8	BULK	SURGE Z	K DAMAGE	K DAMAGE	K	K	K	K	K
REVIOUS	REV IUS	REV SONS	REV SONS	FORWARD	DAMAGE	K	K	K	K	K
(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)
1N4006	0	6.00E+09	1.84E+00	8.20E+19	2.50E+11	1.00E+00	6.19E+06	1.00E-04	8.00E+02	1.00E+02
(1)	0	0	0	0	0	0	0	0	0	0
1N4148	0	1.58E+09	1.68E+00	1.54E+09	1.20E+12	9.00E-01	1.00E-07	1.00E-04	7.50E+01	2.10E+01
(1)	0	0	0	0	0	0	0	0	0	0
1N4249	0	4.52E+10	3.62E+00	4.13E+10	1.30E+11	1.00E+00	1.00E-07	1.00E-04	1.00E+03	2.10E+01
(1)	0	0	0	0	0	0	0	0	0	0
1N457	0	7.40E+12	1.36E+00	2.70E+10	5.60E+12	8.50E-01	4.91E-07	1.00E-04	2.10E+02	2.10E+01
(1)	0	4.00E+01	6.00E+01	0	0	0	0	0	0	0
1N458	0	9.42E+12	1.41E+00	2.00E+11	4.00E+12	8.00E-01	5.84E-07	1.00E-04	1.50E+02	2.10E+01
(1)	0	6.30E+02	0	0	0	0	0	0	0	0
1N459	0	3.60E+11	1.30E+00	2.40E+11	1.20E+11	8.00E-01	5.84E-07	1.00E-04	2.30E+02	8.30E+01
(1)	0	0	0	0	0	0	0	0	0	0
1N461	0	9.42E+12	1.30E+00	2.40E+11	4.00E+12	8.50E-01	1.00E-07	1.00E-04	2.00E+02	3.60E+00
(1)	0	0	0	0	0	0	0	0	0	0
1N461	0	9.42E+12	1.30E+00	2.40E+11	4.00E+12	8.50E-01	1.00E-07	1.00E-04	3.50E+01	2.10E+01
(1)	0	0	0	0	0	0	0	0	0	0

DIODE DEVICE LIBRARY (Cont'd)

PAGE 11

DIODE DEVICE LIBRARY (Cont'd)

DEVICE NAME	IS	MD	RDL	CDO	VDD1	TD	IPOD	VB	SURGE Z	*ITRAC REF)
(ITRAC FLAG)	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----
N-BULK	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----
FWARD	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----
(REF)	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----	+-----
1N600	6 1.00E-13	6 1.00E+00	6 1.00E+07	6 1.00E-09	6 1.00E+00	6 1.00E-12	6 1.00E-04	6 4.70E+00	6 7.00E-02	6 -----
(1)	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----
1N63	6 2.87E-13	6 9.0E-01	6 1.00E+06	6 1.41E-10	6 5.00E-01	6 1.59E-07	6 1.00E-04	6 1.00E+02	6 2.10E+01	6 -----
(1)	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----
1N645	6 4.52E-10	6 1.62E+00	6 4.13E+10	6 1.30E-11	6 8.00E-01	6 1.86E-06	6 1.00E-04	6 2.25E+02	6 1.75E+03	6 (61)
(1)	6 2.25E+01	6 6.9E+03	6 6.90E+03	6 1.49E-04	6 6.65E-01	6 6.60E-02	6 2.80E+00	6 3.63E+00	6 7.90E+01	6 (13)
	6 (34)	6 (66)	6 (66)	6 (60)	6 (60)	6 (60)	6 (17)	6 (21)	6 (13)	
1N6458	6 5.20E-10	6 1.64E+00	6 8.50E+08	6 2.46E-08	6 8.00E-01	6 1.86E-06	6 1.00E-04	6 2.25E+02	6 2.10E+01	6 -----
(1)	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----
1N645Y	6 5.20E-10	6 1.64E+00	6 2.70E+10	6 2.20E-12	6 8.00E-01	6 1.86E-06	6 1.00E-04	6 2.25E+02	6 8.70E+00	6 -----
(1)	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----
1N652	6 5.20E-10	6 1.64E+00	6 2.70E+10	6 1.30E-12	6 8.00E-01	6 1.86E-06	6 1.00E-04	6 2.25E+02	6 8.70E+00	6 -----
(1)	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----
1N646	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 -----
(1)	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----
1N646W	6 2.20E-10	6 1.43E+00	6 3.10E+10	6 1.60E-11	6 1.00E+00	6 9.63E-07	6 1.00E-04	6 1.44E+02	6 2.10E+01	6 -----
(1)	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----	6 +-----

DIODE DEVICE LIBRARY (Cont'd)

240

DEVICE NAME	15	MD	RDL	CDD	VDBI	TD	IPPD	VB	SURGE Z	TRAC REF
ETRAC FLAG	0	-----	+	-----	+	-----	+	-----	+	-----
R_BULK	0	SURGE Z	0	K DAMAGE	0	K DAMAGE	0	K	0	K
FURAWI	0	REVIOUS	0	REV SONS	0	REV SONS	0	K	0	K
(REF)	0	(REF)	0	(REF)	0	(REF)	0	(REF)	0	(REF)
INet46X	0	1.00E-08	0	2.28E+00	0	3.10E+10	0	1.60E-11	0	1.00E+00
(1)	0	-----	+	-----	+	-----	+	-----	+	-----
INet46Y	0	2.20E-10	0	1.43E+00	0	3.10E+10	0	1.60E-11	0	1.00E+00
(1)	0	-----	+	-----	+	-----	+	-----	+	-----
INet46Z	0	1.00E-08	0	2.28E+00	0	3.10E+10	0	1.60E-11	0	1.00E+00
(1)	0	-----	+	-----	+	-----	+	-----	+	-----
INet47	0	1.60E-09	0	1.76E+00	0	4.20E+10	0	7.70E-12	0	1.00E+00
(1)	0	-----	+	-----	+	-----	+	-----	+	-----
INet48	0	2.80E-09	0	1.64E+00	0	5.80E+10	0	6.60E-12	0	1.00E+00
(1)	0	-----	+	-----	+	-----	+	-----	+	-----
INet49	0	4.52E-10	0	1.62E+00	0	4.13E+10	0	1.30E-11	0	1.00E+00
(1)	0	-----	+	-----	+	-----	+	-----	+	-----
INet49X	0	1.60E-11	0	1.15E+00	0	3.60E+10	0	1.20E-11	0	9.00E-01
(1)	0	-----	+	-----	+	-----	+	-----	+	-----
INet49X	0	7.60E-08	0	2.58E+00	0	3.60E+00	0	1.20E-11	0	9.00E-01
(1)	0	-----	+	-----	+	-----	+	-----	+	-----

DIODE DEVICE LIBRARY (Cont'd.)

PAGE 14

DEVICE NAME	1.5	MD	ROL	CGG	VDBI	ID	IPPD	VB	SURGE Z	(TRAC REF)
(TRAC FLAG)	0	-----	*	-----	*	-----	*	-----	*	-----
BULK	0	SURGE Z	*	K DAMAGE	*	K DAMAGE	*	K	*	-----
FURASD	0	REVIOUS	*	REV SONS	*	REV 2SONS	*	K	*	K
(REF)	0	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)
1N642Y	0	1.60E-11	*	1.15E+00	*	3.60E+10	*	8.60E-12	*	9.00E-01
(1)	0	-----	*	-----	*	-----	*	-----	*	-----
1N642Z	0	7.60E-06	*	2.56E+00	*	3.60E+10	*	8.60E-12	*	9.00E-01
(1)	0	-----	*	-----	*	-----	*	-----	*	-----
1N650	0	3.90E-09	*	1.76E+00	*	6.10E+09	*	1.80E-12	*	1.00E+00
(1)	0	-----	*	-----	*	-----	*	-----	*	-----
1N659	0	1.60E-11	*	1.15E+00	*	5.60E+08	*	2.12E-11	*	8.00E-01
(1)	0	-----	*	-----	*	-----	*	-----	*	-----
1N660	0	4.80E-09	*	1.82E+00	*	9.90E+06	*	3.40E-12	*	9.00E-01
(1)	0	-----	*	-----	*	-----	*	-----	*	-----
1N661	0	3.24E-17	*	9.90E-01	*	2.00E+07	*	3.82E-12	*	5.00E-01
(1)	0	-----	*	-----	*	-----	*	-----	*	-----
1N665	0	7.60E-07	*	1.55E+00	*	3.2CE+05	*	7.00E-13	*	6.00E-01
(1)	0	-----	*	-----	*	-----	*	-----	*	-----
1N706	0	1.39E-13	*	1.12E+00	*	1.00E+16	*	2.50E-10	*	9.00E-01
(1)	0	-----	*	-----	*	-----	*	-----	*	-----

DIODE DEVICE LIBRARY (Cont'd.)

PAGE 16

DEVICE NAME	I _S	N _D	R _{DL}	C _{DC}	V _{D81}	T _O	I _{PPD}	V _B	SURGE Z	(TRAC REF)
(TRAC FLAG)	0	0	0	0	0	0	0	0	0	0
R BULK	0	0	0	0	0	0	0	0	0	0
F FORWARD	0	0	0	0	0	0	0	0	0	0
(REF)	0	0	0	0	0	0	0	0	0	0
1N753A	0 1.39E-13	0 1.12E+00	0 1.00E+18	0 1.00E-18	0 9.00E-01	0 1.00E-07	0 1.00E-04	0 6.20E+00	0 4.00E-01	0
(1)	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0
1N754A	0 1.39E-13	0 1.12E+00	0 1.00E+18	0 1.00E-18	0 9.00E-01	0 1.00E-07	0 1.00E-04	0 6.80E+00	0 2.10E+01	0
(1)	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0
1N755A	0 7.26E-10	0 1.73E+00	0 1.00E+09	0 5.00E+12	0 1.00E+00	0 1.00E-08	0 1.00E-03	0 7.50E+00	0 5.00E+00	0
(1)	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0
1N756	0 1.39E-13	0 1.12E+00	0 1.00E+18	0 1.00E-18	0 9.00E-01	0 1.00E-07	0 1.00E-04	0 8.20E+00	0 2.10E+01	0
(1)	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0
1N756A	0 1.39E-13	0 1.12E+00	0 1.00E+18	0 1.00E-18	0 9.00E-01	0 1.00E-07	0 1.00E-04	0 8.20E+00	0 2.10E+01	0
(1)	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0
1N758	0 1.39E-13	0 1.12E+00	0 1.00E+18	0 1.00E-18	0 9.00E-01	0 1.00E-07	0 1.00E-04	0 1.00E+01	0 2.10E+01	0
(1)	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0
1N758A	0 1.39E-13	0 1.12E+00	0 1.00E+18	0 1.00E-18	0 9.00E-01	0 1.00E-07	0 1.00E-04	0 1.00E+01	0 2.10E+01	0
(1)	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0
1N758A1	0 4.20E-14	0 1.10E+00	0 2.20E+09	0 5.38E-10	0 9.00E-01	0 1.26E-07	0 1.00E-04	0 1.00E+01	0 2.10E+01	0
(1)	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0 0.00E+00	0

DIODE DEVICE LIBRARY (Cont'd)

PAGE 17

DEVICE NAME	M	MD	ROL	CDU	VDR1	TD	IPPD	VB	SURGE 1	SURGE 2
(TRAC FLAG)	*	K	BULK	*	SURGE 2	K DAMAGE	K DAMAGE	K	K	K
REVIOUS	*	KV1US	REV1US	REV1US	REV1US	REV1US	REV1US	K	K	K
(REF)	*	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)
IN758A2	0	7.50E-15	0	1.00E+00	0	1.00E+10	0	3.58E-10	0	9.00E-01
{1}	0	-	-	-	-	-	-	-	-	-
IN758A3	0	6.30E-15	0	1.01E+00	0	9.80E+09	0	3.95E-10	0	9.00E-01
{1}	0	-	-	-	-	-	-	-	-	-
IN758A4	0	1.60E-14	0	1.03E+00	0	9.40E+09	0	3.66E-10	0	9.00E-01
{1}	0	-	-	-	-	-	-	-	-	-
IN758A5	0	1.60E-14	0	1.03E+00	0	8.90E+09	0	3.69E-10	0	9.00E-01
{1}	0	-	-	-	-	-	-	-	-	-
IN758A6	0	1.80E-14	0	1.15E+00	0	6.50E+09	0	3.37E-10	0	9.00E-01
{1}	0	-	-	-	-	-	-	-	-	-
IN758A7	0	9.42E-12	0	1.20E+00	0	2.40E+11	0	4.00E+12	0	8.50E-01
{1}	0	-	-	-	-	-	-	-	-	-
IN616W	0	1.20E-13	0	1.12E+00	0	1.00E+18	0	1.00E+18	0	9.00E-01
{1}	0	-	-	-	-	-	-	-	-	-
IN623	0	7.50E-12	0	1.36E+00	0	1.20E+10	0	1.30E+12	0	8.00E-01
{1}	0	-	-	-	-	-	-	-	-	-
IN603	0	7.50E-12	0	1.36E+00	0	1.20E+10	0	1.30E+12	0	4.23E-08
{1}	0	-	-	-	-	-	-	-	-	-

DIODE DEVICE LIBRARY (CONT'D)

DEVICE NAME	15	16	RDL	COD	VDR1	TO	IPOD	VB	SOURCE 1	SOURCE 2	(TRC REF)
(TSAC FLAG)	0	0	0	0	0	0	0	0	0	0	0
R BULK	0	0	0	0	0	0	0	0	0	0	0
F FORWARD	0	0	0	0	0	0	0	0	0	0	0
F REV IODS	0	0	0	0	0	0	0	0	0	0	0
F REV IODS > REV IODS	0	0	0	0	0	0	0	0	0	0	0
(REF)	0	0	0	0	0	0	0	0	0	0	0
(REF) > (REF)	0	0	0	0	0	0	0	0	0	0	0
IN4006	0	5.20E+09	0	1.28E+00	0	8.90E+06	0	1.20E+12	0	8.00E+01	0
(1)	0	0	0	0	0	0	0	0	0	0	0
IN4014	0	1.58E+09	0	1.68E+00	0	1.54E+09	0	1.20E+12	0	9.00E+01	0
(1)	0	0	0	0	0	0	0	0	0	0	0
IN4048	0	8.70E+10	0	1.61E+00	0	1.10E+06	0	2.40E+12	0	9.00E+01	0
(1)	0	0	0	0	0	0	0	0	0	0	0
IN41481	0	8.51E+09	0	2.62E+00	0	4.60E+08	0	1.14E+12	0	1.00E+00	0
(1)	0	0	0	0	0	0	0	0	0	0	0
IN41482	0	1.10E+08	0	4.09E+00	0	5.25E+08	0	1.28E+12	0	8.20E+01	0
(1)	0	0	0	0	0	0	0	0	0	0	0
IN41483	0	1.10E+08	0	2.05E+00	0	5.60E+08	0	9.60E+15	0	1.00E+00	0
(1)	0	0	0	0	0	0	0	0	0	0	0
IN41484	0	1.05E+08	0	2.03E+00	0	4.80E+08	0	1.18E+12	0	9.50E+01	0
(1)	0	0	0	0	0	0	0	0	0	0	0
IN41485	0	1.15E+08	0	2.04E+00	0	5.70E+08	0	1.23E+12	0	9.50E+01	0
(1)	0	0	0	0	0	0	0	0	0	0	0

PAGE 18

DIODE DEVICE LIBRARY (Cont'd)

PAGE 19

DEVICE NAME	I _S	N _D	R _{D1}	C _{D1}	V _{D1}	T _D	I _{PPD}	V _B	SURGE Z	(TRAC REF)
IN914B6	1.55E-08	2.06E+00	6.30E+08	1.11E-12	9.50E-01	2.87E-09	1.00E-04	7.50E+01	2.10E+01	*
(TRAC FLAG)	*	*	*	*	*	*	*	*	*	*
R_BULK	*	*	*	*	*	*	*	*	*	K
SURGE_Z	*	*	*	*	*	*	*	*	*	K
(1)	*	*	*	*	*	*	*	*	*	*
REVIOUS	*	*	*	*	*	*	*	*	*	*
REV_SONS	*	*	*	*	*	*	*	*	*	*
FORWARD	*	*	*	*	*	*	*	*	*	*
(REF)	*	*	*	*	*	*	*	*	*	(REF)
(REF)	*	*	*	*	*	*	*	*	*	(REF)
*	*	*	*	*	*	*	*	*	*	*
IN916B3	1.39E-13	1.12E+00	1.00E+18	3.29E-10	9.50E-01	2.02E-03	1.00E-04	1.20E+01	1.03E+02	*
(1)	*	*	*	*	*	*	*	*	*	*
(C)	*	*	*	*	*	*	*	*	*	*
IN965B	1.39E-13	1.12E+00	1.00E+18	1.00E-18	9.50E-01	1.00E-07	1.00E-04	1.50E+01	2.10E+01	*
(1)	*	*	*	*	*	*	*	*	*	*
(C)	*	*	*	*	*	*	*	*	*	*
IN967B	1.39E-13	1.12E+00	1.00E+18	1.00E-18	9.50E-01	1.00E-07	1.00E-04	1.80E+01	1.90E+00	*
(1)	*	*	*	*	*	*	*	*	*	*
(C)	*	*	*	*	*	*	*	*	*	*
IN971B	1.39E-13	1.12E+00	1.00E+18	1.00E-18	9.50E-01	1.00E-07	1.00E-04	3.30E+01	2.10E+01	*
(1)	*	*	*	*	*	*	*	*	*	*
IN995	1.30E-07	1.43E+00	4.00E+06	5.66E-12	5.00E-01	2.53E-08	1.00E-04	1.50E+01	2.10E+01	*
(1)	*	*	*	*	*	*	*	*	*	*

TRANSISTOR DEVICE LIBRARY

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 2

DEVICE NAME	HFEI	TN	TI	ICS	MC	CCU	VCBI	RCL	IES
(TRAC FLAG)	+ - - - -	+ - - - -	+ - - - -	+ - - - -	+ - - - -	+ - - - -	+ - - - -	+ - - - -	+ - - - -
ME	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -
CEO	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -
BULK RESISTANCE	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -
C-B	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -
(REF)	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -
K FORWARD	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -
C-B	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -
(REF)	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -	- - - - -
2N1016B	2.87E+01	7.49E+00	2.03E-07	1.76E-06	8.22E-10	1.11E+00	1.75E-09	7.00E-01	1.00E+07
(1)	1.02E+00	4.00E-10	1.00E+00	1.00E+07	1.00E-03	1.00E-05	1.00E+02	2.50E+01	2.10E+01
2N1016E	1.60E+01	4.79E+00	3.29E-07	2.40E-06	1.87E-10	1.03E+00	1.85E-09	7.00E-01	1.00E+07
(1)	9.72E+01	3.91E-10	8.00E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+02	2.50E+01	2.10E+01
2N1037	9.00E+00	9.00E+00	5.31E-07	1.59E-06	1.00E-06	9.94E-01	9.19E-11	5.00E-01	1.00E+07
(1)	9.94E-01	1.41E-10	5.00E-01	1.00E+07	1.00E-03	1.00E-05	5.00E+01	2.00E+01	2.10E+01
2N1039	1.00E+01	5.00E+00	1.99E-05	1.59E-04	6.00E-09	9.94E-01	2.12E-10	5.00E-01	1.00E+07
(1)	9.94E-01	1.41E-09	5.00E-01	1.00E+07	1.00E-03	1.00E-05	6.00E+01	2.00E+01	2.10E+01

DEVICE NAME	HFB1	HFB1	TN	T1	TCS	MC	CCU	VCB1	RCL	IES
(TRAC FLAG)	*	*	-	-	-	-	-	-	-	-
ME	*	*	CEO	*	REL	*	IPPE	E-BBOV	SURGE ZC	SURGE ZE
BULK RESISTANCE	*	*	-	Z SURGE C-B	*	-	-	-	-	*
C-B (REF)	E-B	*	1US	10US	E-B	SURGE E-B	DAMAGE K (<50%)	DAMAGE K (>50%)	D-B (REF)	E-B
K FORWARD	E-B	*	K	*	*	*	10US	E-B	C-B (REF)	E-B
C-B (REF)	E-B	*	C-B	E-B	*	K	*	*	*	*
			(REF)		(REF)		(REF)	(REF)	(REF)	
2N1042RA	*	*	*	*	*	*	*	*	*	*
(C)	*	*	*	*	*	*	*	*	*	*
1.60E-01	2.95E-01	*	5.92E+02	2.63E+02	*	2.55E+02	5.00E+02	3.11E-04	2.69E-04	1.20E+00
(34)	(34)	*	(34)	(34)	*	(34)	(34)	(60)	(60)	
1.60E-01	1.40E-01	*	0	0	*	0	0	0	0	*
(60)	(60)	*	(60)	(60)	*	0	0	0	0	*
2N1099	8.40E+00	*	2.20E+00	6.52E-07	*	1.03E-06	2.23E-14	*	1.30E+00	1.20E-09
(1)	1.90E+00	*	1.50E-09	6.00E-01	*	1.00E+07	1.00E-03	*	8.00E+01	4.00E+02
		*			*			*		*
2N1132	5.60E+01	*	7.96E-09	3.18E-08	*	4.00E-12	1.39E+00	*	5.92E-11	9.36E-01
(0)	1.42E+00	*	4.06E+11	1.6E+00	*	1.00E+07	1.00E-03	*	5.00E+01	5.00E+00
		*			*			*		*
2N1184	6.80E+01	*	7.47E+00	7.69E-08	*	1.50E-07	1.13E-05	*	9.68E-01	2.40E-10
(1)	8.23E-01	*	2.00E-10	4.07E-01	*	1.03E+07	1.00E-03	*	4.50E+01	2.00E+02
		*			*			*		*

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 4

DEVICE NAME	IN	T1	LCS	MC	CCD	VCBI	RCL	IES
HFE1	+	-	+	-	+	-	-	-
ME	+	-	+	-	+	-	-	-
(TRAC FLAG)	+	+	+	+	+	+	SURGE 2C	+
CEO	+	+	REL	IPPE	C-BBDV	E-BBOV	-	-
BULK RESISTANCE	+	+	-	-	-	-	-	-
C-B E-B	+	Z SURGE C-B	+	Z SURGE E-B	DAMAGE K (>50NS)	DAMAGE K (<50NS)	-	-
(REF)	+	IUS	IUS	IUS	C-B	E-B	C-B	E-B
K FORWARD	+	K	K	K	(REF)	(REF)	(REF)	(REF)
C-B E-B	+	C-B	E-B	C-B	E-B	E-B	K	K
(REF)	+	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)
2N1184 T	6.80E+01	7.47E+00	7.69E-08	1.50E-07	1.13E-05	9.68E-01	2.40E-10	4.00E-01
(1)	8.23E-01	2.00E-10	4.00E-01	1.00E+07	1.00E-03	1.00E-05	4.50E+01	2.00E+01
2.00E-01	3.00E-01	(32)	1.40E+02	(32)	2.00E+02	(32)	6	6
3.00E+01	1.05E+00	1.12E-09	5.00E-07	1.00E+00	1.11E-12	4.00E-01	1.00E+07	8.12E-06
4.	3.00E+01	3.50E-01	9.62E-09	1.12E-07	5.00E-07	1.11E+00	3.10E-12	4.00E-01
(1)	1.05E+00	3.30E-12	5.00E-01	1.00E+07	1.00E-03	1.00E-05	4.00E+01	2.10E+01
2N1225	3.00E+01	1.05E+00	9.62E-09	1.12E-07	5.00E-07	1.11E+00	3.10E-12	4.00E-01
(1)	1.05E+00	3.30E-12	5.00E-01	1.00E+07	1.00E-03	1.00E-05	4.00E+01	2.10E+01
2N1289	2.00E+01	9.00E+00	3.98E-09	1.59E-08	6.00E-09	9.94E-01	1.41E-11	5.00E-01
(1)	9.94E-01	1.41E-11	5.00E-01	1.00E+07	1.00E-03	1.00E-05	6.00E+01	2.10E+01
2N1301	1.50E+01	5.00E+00	4.55E-09	1.59E-08	1.02E-10	9.94E-01	1.70E-11	5.00E-01
(1)	9.94E-01	1.41E-11	5.00E-01	1.00E+07	1.00E-03	1.00E-05	6.00E+01	2.10E+01

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 5

DEVICE NAME	HFEN	HFEI	IN	TI	ICS	MC	CCO	VCB1	RCL	IES
(TRAC FLAG)	-	-	-	-	-	-	-	-	-	-
ME	-	-	-	-	-	-	-	-	-	-
CEO	-	-	VERI	REL	IPPC	IPPE	C-BBDV	SURGE ZC	SURGE ZE	-
BULK RESISTANCE	-	-	-	-	-	-	-	DAMAGE K (>50NS)	DAMAGE K (>50NS)	-
C-B	E-B	IUS	SURGE C-B	IUS	IUS	SURGE E-B	C-B	E-B	C-B	E-B
(RtF)	-	-	(REF)	-	-	(REF)	(REF)	(REF)	(REF)	-
K FORWARD	-	-	-	-	-	-	-	-	-	-
C-B	E-B	C-B	E-B	C-B	K	E-B	(REF)	(REF)	K	-
(REF)	-	-	(REF)	-	-	(REF)	-	-	-	-
2N1304	7.00E+01	5.00E+00	1.99E-08	7.96E-08	3.50E-07	1.49E+00	2.53E-11	1.40E+00	1.00E+07	3.43E-07
(1)	1.51E+00	8.45E-12	1.40E+00	1.00E+07	1.00E-03	1.00E-05	2.50E+01	2.50E+01	2.10E+01	2.10E+01
44	1.00E+02	5.00E+00	1.33E-08	7.96E-08	3.50E-07	1.49E+00	2.53E-11	1.40E+00	1.00E+07	3.43E-07
(1)	1.51E+00	8.45E-12	1.40E+00	1.00E+07	1.00E-03	1.00E-05	2.50E+01	2.50E+01	2.10E+01	2.10E+01
2N1306	1.00E+02	5.00E+00	1.33E-08	7.96E-08	3.50E-07	1.49E+00	2.53E-11	1.40E+00	1.00E+07	3.43E-07
(1)	1.51E+00	8.45E-12	1.40E+00	1.00E+07	1.00E-03	1.00E-05	2.50E+01	2.50E+01	2.10E+01	2.10E+01
2N1307	1.00E+02	5.00E+00	1.33E-08	7.96E-08	3.50E-07	1.49E+00	2.53E-11	1.40E+00	1.00E+07	3.43E-07
(1)	1.51E+00	5.92E-12	1.40E+00	1.00E+07	1.00E-03	1.00E-05	3.00E+01	2.50E+01	2.10E+01	2.10E+01
2N1308	1.50E+02	5.00E+00	1.33E-08	7.96E-08	3.50E-07	1.49E+00	2.53E-11	1.40E+00	1.00E+07	3.43E-07
(1)	1.51E+00	8.45E-12	1.40E+00	1.00E+07	1.00E-03	1.00E-05	2.50E+01	2.50E+01	2.10E+01	2.10E+01

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 6

DEVICE NAME	HFET	HEF1	TN	T1	IGS	MC	CCD	VCBI	RCL	IES
(TFAC FLAG)	+	---	+	---	+	---	+	---	+	-
HE	o	CEU	o	VEBI	o	IPPC	o	E-BODY	o	SURGE ZC
BULK RESISTANCE	+	+	+	REL	+	+	+	+	+	SURGE ZE
C-B (REF)	o	E-B	o	Z SURGE C-B	o	Z SURGE E-B	o	DAMAGE K (<SONS)	o	DAMAGE K (>SONS)
K FORWARD	o	E-B	o	IUS (REF)	o	IUS (REF)	o	E-B (REF)	o	C-B (REF)
C-B (REF)	o	E-B	o	K	o	K	o	K	o	K
2N1342	o	4.31E+01	o	5.00E-01	o	1.56E-09	o	3.33E-07	o	1.66E-13
(11)	o	9.92E-01	o	3.70E-11	o	8.00E-01	o	1.00E-03	o	1.05E+00
2N1401G	o	1.00E+02	o	5.00E+01	o	1.99E-05	o	1.59E-04	o	6.00E-09
(11)	o	9.94E-01	o	1.41E-09	o	5.00E-01	o	1.00E-07	o	9.94E-01
2N1403	o	1.00E+01	o	5.00E+00	o	1.27E-07	o	1.59E-06	o	6.98E-15
(11)	o	9.94E-01	o	2.47E-10	o	5.00E-01	o	1.00E-03	o	2.47E-10
2N1405	o	7.96E+01	o	3.69E+00	o	5.92E-08	o	3.70E-07	o	4.57E-12
(11)	o	1.05E+00	o	2.30E-10	o	9.00E-01	o	1.00E+07	o	9.68E-01

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 7

TRANSISTOR DEVICE LIBRARY (Cont'd).

PAGE 8

DEVICE NAME	HFE1	TN	TI	ICS	MC	CCD	VCS1	RCI	IES
(TRAC FLAG)	0	0	0	0	0	0	0	0	0
ME	0	CEO	0	VERI	0	IPPC	0	E-BBDY	SURGE IC SURGE ZE
BULK RESISTANCE	0	0	0	Z SURGE (~B)	0	IPPE	0	0	0
C-B E-B	0	0	IUS	10US	0	SURGE E-B	0	DAMAGE K (<SONS)	DAMAGE K (>SONS)
(REF)	0	0	(REF)	0	0	10US	0	C-B E-B	C-B E-B
K FORWARD	0	0	K	K	0	(REF)	0	(REF)	(REF)
C-B (REF)	0	0	C-B	E-B	0	(REF)	0	K	0
2N158	2.86E+01	3.00E-01	8.12E-10	3.34E-07	1.17E-13	1.01E+00	4.60E-11	8.00E-01	1.00E+07
(1)	0.01E+00	1.55E-10	9.00E-01	1.00E-07	1.00E-03	1.00E-05	6.00E-01	3.00E-01	2.10E+01
2N1613	8.00E+01	5.00E+00	1.77E-08	7.96E-09	4.00E-11	1.19E+00	2.59E-11	1.68E+00	1.00E+07
(1)	1.21E+00	5.44E-11	7.13E-01	1.00E-07	1.00E-03	1.00E-05	7.50E+01	7.00E+00	6.05E+01
2N1709	2.50E+01	2.50E-01	1.54E-09	1.10E-06	3.15E-12	1.11E+00	1.02E-10	8.00E-01	1.00E+07
(1)	1.05E+00	4.20E-10	0	1.00E+00	1.00E-07	1.00E-03	1.00E-05	7.50E+01	4.00E+00
2N1711	1.35E-02	0	2.27E-09	7.96E-09	1.00E-08	2.49E+00	3.54E-11	5.00E-01	1.00E+07
(0)	2.67E+00	1.13E-10	0	5.00E-01	1.00E-01	1.00E-03	1.00E-05	7.50E+01	7.00E+00

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 9

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 10

DEVICE NAME	HFF1	o	HFF1	o	TN	o	T1	o	I _C	o	M _C	o	CCD	o	RCL	o	IES			
(TRAC FLAG)	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*			
ME	*	*	CEL	*	VEL1	*	REL	*	IPPC	*	IPPE	*	C-BBDV	*	E-BBDV	*	SURGE ZE			
BULK RESISTANCE	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	DAMAGE K (>50NS)			
C-B	*	*	E-B	*	I _{US}	*	Z SURGE C-B	*	E-B	*	I _{US}	*	10US	*	C-B	*	E-B			
(REF)	*	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)			
K FORWARD	*	*	E-B	*	K	*	E-B	*	C-B	*	K	*	E-B	*	K	*	K			
C-B	*	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)			
2N1900	o	1.36E+02	o	1.37E+00	o	1.69E-09	o	1.08E-06	o	2.32E-11	o	1.02E+00	o	1.80E-09	o	7.00E-01	o	1.00E+07	o	1.60E-11
(1)	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*
1.02E+00	o	7.00E-09	o	8.00E-03	o	1.00E+07	o	1.00E-05	o	1.40E+02	o	5.00E+00	o	2.10E+01	o	2.10E+01	o	2.10E+01	o	
2N2046	o	2.50E+01	o	9.00E+00	o	6.12E-10	o	1.59E-08	o	4.00E-09	o	9.94E-01	o	2.12E-12	o	5.00E-01	o	1.00E+07	o	4.00E-09
(1)	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*
9.94E-01	o	7.07E-12	o	5.00E-01	o	1.00E+07	o	1.00E-03	o	1.00E-05	o	2.00E+01	o	2.00E+00	o	2.10E+01	o	2.10E+01	o	
2N2060	o	1.00E+00	o	2.00E-01	o	8.00E-10	o	6.17E-07	o	1.20E-13	o	1.08E+00	o	3.48E-11	o	9.00E-01	o	1.30E+07	o	2.60E-13
(1)	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*
1.01E+00	o	6.60E-11	o	6.00E-01	o	1.40E+07	o	1.00E-03	o	1.00E-05	o	1.00E+02	o	7.00E+00	o	2.10E+01	o	2.10E+01	o	
2N2077	o	2.00E+01	o	9.00E+00	o	1.06E-09	o	3.18E-09	o	1.62E-12	o	9.94E-01	o	1.70E-11	o	5.00E-01	o	1.00E+07	o	4.86E-14
(1)	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*
9.94E-01	o	9.90E-11	o	5.00E-01	o	1.00E+07	o	1.00E+07	o	1.00E-05	o	1.20E+02	o	5.00E+00	o	2.10E+01	o	2.10E+01	o	

TRANSITOR SERVICE LIBRARY (Cont'd)

DRAFT 10

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 12

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 13

DEVICE NAME	HFEN	HFE1	TN	Y1	I _C S	M _C	C _{CD}	V _{CB1}	R _{CL}	IES
(TKAC FLAG)	+	+	-----	+	-----	+	-----	+	-----	-----
ME	o	CEO	o	REL	o	IPPE	o	E-BBDV	o	SURGE ZC
BULK RESISTANCE	o	-----	+	-----	+	-----	+	-----	+	SURGE ZE
C-B	o	E-B	o	I _{BS}	o	Z SURGE E-B	o	DAMAGE K (<50NS)	o	DAMAGE K (>50NS)
(REF)	o	-----	+	10US	o	10US	o	C-B	o	-----
K FORWARD	o	-----	+	-----	o	(REF)	o	E-B	o	E-B
C-B	o	E-B	o	C-B	o	K	o	(REF)	o	(REF)
(REF)	o	-----	+	-----	+	-----	+	-----	+	-----
2N2243	6.99E+01	3.14E+00	9.59E-10	2.65E-07	7.53E-14	9.77E-01	3.00E-11	8.00E-01	1.00E+07	5.63E-14
(1)	9.77E-01	6.70E-11	6.00E-01	1.00E+07	1.00E-03	1.00E-05	1.20E+02	7.00E+00	2.10E+01	2.10E+01
2N2270	1.00E+01	9.00E+00	1.27E-07	1.59E-06	6.98E-15	9.94E-01	2.47E-10	5.00E-01	1.00E+07	6.98E-15
(1)	9.94E+01	2.47E-10	5.00E-01	1.00E+07	1.00E-03	1.00E-05	6.00E+01	7.00E+00	2.10E+01	2.10E+01
2N2368	4.25E+01	1.00E+00	2.93E-10	2.25E-08	4.00E-12	1.20E+00	8.20E-12	1.00E+00	1.00E+07	5.11E-15
(1)	9.77E-01	4.90E-12	1.00E+00	1.00E+07	1.00E-03	1.00E-05	4.00E+01	4.50E+00	2.10E+01	2.10E+01
2N2369	4.50E+01	1.00E+00	3.18E-10	3.18E-09	2.26E-10	1.65E+00	2.63E-12	1.10E+00	1.00E+07	4.99E-15
(0)	1.04E+00	2.58E-12	1.06E+00	1.00E+07	1.00E-03	1.00E-05	4.00E+01	4.50E+00	2.10E+01	2.10E+01

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 14

DEVICE NAME	HFE1	IN	T1	I1S	MC	CCD	VCBI	RCL	IES
(TRAC FLAG)	*	*	-	-	-	-	-	-	-
ME	*	VEE1	*	REL	*	IPPE	*	C-BBDY	SURGE ZC
BULK RESISTANCE	*	*	*	*	*	*	*	E-BBDY	SURGE ZE
C-B (REF)	*	BULK	SURGE C-B	*	Z SURGE E-B	*	DAMAGE K (<50A5)	DAMAGE K (>50A5)	*
K FOR KAO	*	*	1US	10US	1US	10US	C-B	C-B	E-B
C-B (Rtf)	*	(REF)	*	(REF)	*	(REF)	(REF)	(REF)	(REF)
2N2411	2.86E+01	4.10E-01	6.76E-10	5.24E-08	1.75E-15	9.82E-01	5.30E-12	8.00E-01	1.00E+07
(1)	9.82E-01	5.60E-12	9.00E-07	1.00E+07	1.00E-03	1.00E-05	2.50E+01	5.00E+00	2.10E+01
53	5.78E+01	2.00E-02	4.03E-10	3.36E-09	1.86E-12	1.05E+00	4.00E-12	8.00E-01	1.00E+07
(1)	9.44E-01	5.50E-12	6.00E-01	1.00E+07	1.00E-03	1.00E-05	4.00E+01	5.00E+00	2.10E+01
2N2461	1.15E+02	1.50E+00	3.47E-10	2.40E-07	6.00E-13	1.08E+00	6.90E-12	8.00E-01	1.00E+07
(1)	9.44E-01	1.90E-11	9.00E-01	1.00E+07	1.00E-03	1.00E-05	6.00E+01	5.00E+00	2.10E+01
2N2536	9.52E+01	1.00E+00	3.96E-10	3.00E-07	3.00E-14	1.02E+00	5.80E-12	8.00E-01	1.00E+07
(1)	9.68E-01	4.30E-12	9.00E-01	1.00E+07	1.00E-03	1.00E-05	2.50E+01	5.00E+00	2.10E+01
2N2656	9.52E+01	1.00E+00	3.96E-10	3.30E-C7	3.00E-C7	1.02E+00	5.80E-12	8.00E-01	1.00E+07
(1)	9.68E-01	4.30E-12	9.00E-01	1.00E+07	1.00E-03	1.00E-05	2.50E+01	5.00E+00	2.10E+01

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAG. 15

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 16

TRANSISTOR DEVICE LIBRARY (Cont'd)

DEVICE NAME	HEEN	HFEI	1N	11	1CS	MC	CCC	VCB1	RCL	IES
(TRAC FLAG)	ME	CEO	VEBI	REL	IPPC	IPPE	E-BBDY	E-BBDY	SURGE ZC	SURGE ZE
BULK RESISTANCE	E-E	1US	2 SURGE C-B	10US	1US	7 SURGE E-B	10US	DAMAGE K (SONS)	DAMAGE K (SONS)	
(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	C-B	E-B	E-B
K FORWARD	E-B	C-B	K	E-B	C-B	K	E-B	(REF)	(REF)	(REF)
(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)
2N2887	4.83E+01	3.20E-01	2.84E-10	4.84E-07	1.16E-12	1.04E+00	1.03E-10	8.00E-01	1.00E+07	2.85E-13
(1)	1.04E+00	4.40E-10	9.00E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+02	4.00E+01	2.10E+01	2.10E+01
2N2894	7.00E+01	5.31E-10	3.18E-09	2.11E-12	2.49E+00	3.89E-12	1.01E+00	1.00E+07	1.00E+07	9.40E-13
(0)	1.50E+02	3.44E-12	1.05E+00	1.00E+07	1.00E-03	1.00E-05	1.20E+01	4.00E+00	4.60E+00	1.60E+00
1.95E+00	2.30E+00	4.60E+01	9.35E+02	1.30E+01	1.78E+01	7.78E-06	3.82E-06	3.48E-02	1.71E-02	
(34)	(60)	(34)	(34)	(34)	(34)	(60)	(60)	(60)	(60)	
2N2905	1.33E+02	1.40E+00	4.78E-08	4.664E-08	4.42E-14	1.01E+00	1.45E-11	8.00E-01	1.00E+07	9.82E-15
(1)	9.60E-01	1.80E-11	1.00E+00	1.00E+07	1.00E-03	1.00E-05	6.00E+01	5.00E+00	2.10E+01	2.10E+01
2N2907	2.16E+02	4.20E+00	4.98E-10	3.55E-08	1.48E-13	1.43E+00	2.60E-11	1.00E+00	1.00E+07	2.21E-14
(1)	9.68E-01	2.10E-11	1.00E+00	1.00E+07	1.00E-03	1.00E-05	6.00E+01	5.00E+00	2.10E+01	5.00E+00

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 18

DEVICE NAME	HFE1	I	HFE1	I	T1	I	IC5	I	MC	I	VCB1	I	RCL	I	IES	
(THAC FLAG)	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	
ME	*	*	CEI	*	VERI	*	REF	*	IPPC	*	C-BDV	*	SURGE ZC	*	SURGE ZE	
BULK RESISTANCE	*	*	*	*	SURGE C-B	*	2 SURGE E-B	*	IPPE	*	C-BDV	*	DAMAGE K (50NS)	*	DAMAGE K (50NS)	
(C-B E-B	*	*	*	*	1US	*	1US	*	DAMAG	K	E-B	*	(C-B E-B	*	(C-B E-B	
(REF)	*	*	*	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	
K FORWARDING	*	*	*	*	K	*	K	*	K	*	K	*	K	*	K	
C-B E-B	*	*	*	*	C-B	*	E-B	*	C-B	*	E-B	*	(REF)	*	(REF)	
(XFT)	*	*	*	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	
2N2977	0	1.00E+01	*	5.00E+00	*	3.70E-07	*	1.59E-06	*	5.00E-09	*	9.94E-01	*	1.41E-10	*	5.00E-09
(1)	0	3.94E-01	*	1.41E-10	*	5.00E-01	*	1.00E+07	*	1.00E-03	*	1.00E-05	*	6.00E+01	*	7.30E+01
2N2996	0	2.86E+01	*	4.11E-01	*	6.76E-10	*	5.24E-08	*	1.75E-15	*	9.82E-01	*	5.00E-12	*	8.00E-01
(1)	0	9.62E-01	*	5.60E-12	*	9.00E-01	*	1.00E+07	*	1.00E-03	*	1.00E-05	*	1.50E+01	*	2.10E+01
2N3013	0	6.30E+01	*	2.50E-01	*	1.97E-10	*	7.60E-09	*	1.60E-12	*	1.25E+00	*	3.48E-12	*	9.00E-01
(1)	0	9.92E-01	*	8.01E-12	*	9.00E-01	*	1.00E+07	*	1.00E-03	*	1.00E-05	*	4.00E+01	*	5.00E+00
2N3017	0	6.03E+01	*	4.59E+00	*	1.28E-09	*	8.97E-06	*	8.64E-13	*	9.92E-01	*	1.70E-10	*	9.00E-01
(1)	0	1.02E+00	*	4.80E-10	*	9.00E-01	*	1.00E+07	*	1.00E-03	*	1.00E-05	*	1.00E+02	*	4.00E+00

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 20

DEVICE NAME	REF1
HELN	*
(HELN)	*
CEU	*
BULK RESISTANCE	*
C-B	*
K	*
FUKAKO	*
C-B	*
(REF1)	*
(REF2)	*
(REF3)	*
(REF4)	*
(REF5)	*
(REF6)	*
(REF7)	*
(REF8)	*
(REF9)	*
(REF10)	*
(REF11)	*
(REF12)	*
(REF13)	*
(REF14)	*
(REF15)	*
(REF16)	*
(REF17)	*
(REF18)	*
(REF19)	*
(REF20)	*
(REF21)	*
(REF22)	*
(REF23)	*
(REF24)	*
(REF25)	*
(REF26)	*
(REF27)	*
(REF28)	*
(REF29)	*
(REF30)	*
(REF31)	*
(REF32)	*
(REF33)	*
(REF34)	*
(REF35)	*
(REF36)	*
(REF37)	*
(REF38)	*
(REF39)	*
(REF40)	*
(REF41)	*
(REF42)	*
(REF43)	*
(REF44)	*
(REF45)	*
(REF46)	*
(REF47)	*
(REF48)	*
(REF49)	*
(REF50)	*
(REF51)	*
(REF52)	*
(REF53)	*
(REF54)	*
(REF55)	*
(REF56)	*
(REF57)	*
(REF58)	*
(REF59)	*
(REF60)	*
(REF61)	*
(REF62)	*
(REF63)	*
(REF64)	*
(REF65)	*
(REF66)	*
(REF67)	*
(REF68)	*
(REF69)	*
(REF70)	*
(REF71)	*
(REF72)	*
(REF73)	*
(REF74)	*
(REF75)	*
(REF76)	*
(REF77)	*
(REF78)	*
(REF79)	*
(REF80)	*
(REF81)	*
(REF82)	*
(REF83)	*
(REF84)	*
(REF85)	*
(REF86)	*
(REF87)	*
(REF88)	*
(REF89)	*
(REF90)	*
(REF91)	*
(REF92)	*
(REF93)	*
(REF94)	*
(REF95)	*
(REF96)	*
(REF97)	*
(REF98)	*
(REF99)	*
(REF100)	*
(REF101)	*
(REF102)	*
(REF103)	*
(REF104)	*
(REF105)	*
(REF106)	*
(REF107)	*
(REF108)	*
(REF109)	*
(REF110)	*
(REF111)	*
(REF112)	*
(REF113)	*
(REF114)	*
(REF115)	*
(REF116)	*
(REF117)	*
(REF118)	*
(REF119)	*
(REF120)	*
(REF121)	*
(REF122)	*
(REF123)	*
(REF124)	*
(REF125)	*
(REF126)	*
(REF127)	*
(REF128)	*
(REF129)	*
(REF130)	*
(REF131)	*
(REF132)	*
(REF133)	*
(REF134)	*
(REF135)	*
(REF136)	*
(REF137)	*
(REF138)	*
(REF139)	*
(REF140)	*
(REF141)	*
(REF142)	*
(REF143)	*
(REF144)	*
(REF145)	*
(REF146)	*
(REF147)	*
(REF148)	*
(REF149)	*
(REF150)	*
(REF151)	*
(REF152)	*
(REF153)	*
(REF154)	*
(REF155)	*
(REF156)	*
(REF157)	*
(REF158)	*
(REF159)	*
(REF160)	*
(REF161)	*
(REF162)	*
(REF163)	*
(REF164)	*
(REF165)	*
(REF166)	*
(REF167)	*
(REF168)	*
(REF169)	*
(REF170)	*
(REF171)	*
(REF172)	*
(REF173)	*
(REF174)	*
(REF175)	*
(REF176)	*
(REF177)	*
(REF178)	*
(REF179)	*
(REF180)	*
(REF181)	*
(REF182)	*
(REF183)	*
(REF184)	*
(REF185)	*
(REF186)	*
(REF187)	*
(REF188)	*
(REF189)	*
(REF190)	*

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 21

DEVICE NAME	HFEN	H	HEEL	T	N	T	I	C	S	M	CCC	VCS1	RCL	IES
(TRAC FLAG)	ME	CEO	VERB1	REL	IPPC	IPPE	E-BBDV	E-BBV	SURGE ZC	SURGE ZE				
2N3499	1.08E+02	6.00E-01	5.94E-10	2.25E-07	6.93E-13	1.05E-00	2.40E-11	1.00E+00	1.00E+07	5.35E-14				
(1)	9.92E-01	1.60E-11	1.00E+00	1.00E+07	1.00E-03	1.00E-05	1.00E+02	6.00E+00	2.10E+01	2.10E+01				
2N3509	1.53E+02	2.64E-01	1.29E-10	1.17E-08	4.07E-14	1.01E+00	2.95E-12	9.00E-01	1.00E+07	2.97E-15				
(1)	9.68E-01	3.64E-12	9.00E-01	1.00E+07	1.00E-03	1.00E-05	4.00E+01	6.00E+00	2.10E+01	2.10E+01				
2N3553	3.41E+01	5.34E+00	2.65E-09	3.87E-08	1.97E-14	1.04E+00	2.94E-11	8.00E-01	1.00E+07	1.36E-13				
(1)	1.01E+00	1.04E-10	8.00E-01	1.00E+07	1.00E-03	1.00E-05	6.50E+01	4.00E+00	2.10E+01	2.10E+01				
2N3556	1.50E+01	5.00E+00	5.31E-08	1.99E-07	4.00E-09	9.94E-01	1.98E-11	5.00E-01	1.00E+07	4.00E-09				
(1)	9.94E-01	1.41E-11	5.00E-01	1.00E+07	1.00E-03	1.00E-05	2.00E+01	2.00E+01	2.10E+01	2.10E+01				

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 25

DEVICE NAME	HFE _N	HFE _I	T _N	T _I	I _{C(S)}	I _C	CCC	V _{CB1}	RCL	IES
(TRAC FLAG)	ME	ME	---	+	---	+	---	+	---	+
	CEO	CEO	VEBI	REL	I _{PIC}	IPPE	C-BBDY	E-BBDY	SURGE ZC	SURGE IE
	BULK RESISTANCE	BULK RESISTANCE	Z SURGE (-B)	+	+	+	DAMAGE K (<SONS)	DAMAGE K (>SONS)	DAMAGE K	DAMAGE K
C-B	E-B	E-B	IUS	IUS	IUS	IUS	C-B	E-B	C-B	E-B
(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)
C-E	K	FULKARD	-	-	-	-	-	-	-	-
C-E	E-B	E-B	C-E	E-B	C-B	E-B	K	K	K	K
(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)
2N3564	(0)	(0)	0	0	0	0	0	0	0	0
0.00E+02	2.60E+01	2.15E+03	2.15E+03	2.15E+03	1.30E+00	4.15E+00	{ 34 }	6.93E-11	2.15E+03	1.30E+00
(34)	(60)	(60)	(60)	(60)	(60)	(60)	(60)	(60)	(60)	(60)
1.50E+02	3.20E+02	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0	0
2N3632	(1)	1.02E+01	2.54E+00	1.97E-09	9.83E-08	5.38E-13	1.10E+00	6.93E-11	6.00E-01	1.00E+07
1.02E+00	1.21E+10	8.00E-01	1.00E+07	1.00E+07	1.00E+03	1.00E+05	6.50E+01	4.00E+00	2.10E+01	2.10E+01
0	0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0	0
2N3633	(1)	2.49E+02	1.00E-01	5.28E-11	1.28E-10	7.40E-14	1.08E+00	2.40E-12	1.00E+00	1.00E+07
9.68E+01	1.60E+12	9.00E-01	1.00E+07	1.00E+07	1.00E+03	1.00E+05	1.50E+01	4.00E+00	2.10E+01	2.10E+01
0	0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0	0
2N3723A	(1)	1.60E+01	8.05E-01	9.44E+02	4.02E+03	1.12E+11	1.16E+01	2.24E+11	7.30E-01	1.00E+07
3.88E+02	7.39E+11	7.50E+01	1.00E+07	1.00E+07	1.00E+03	1.00E+05	1.00E+02	6.00E+00	2.10E+01	2.10E+01
0	0	0	0	0	0	0	0	0	0	0
0	0	0	0	0	0	0	0	0	0	0

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 26

DEVICE NAME	HFEI	TN	II	I _S	MC	CCO	V _{CBI}	RCL	IES
(TRAC FLAG)	*	*	*	---	*	---	*	---	*
ME	a	CEO	*	VERB	*	IPPC	*	E-BBDV	SURGE ZC
BULK RESISTANCE	*	*	*	REL	*	IPPE	*	E-BBDV	SURGE ZC
C-B	E-B	E-B	*	Z SURGE	C-B	---	*	---	*
(REF)	*	*	*	10S	10US	*	Z SURGE E-B	*	DAMAGE K (>SONS)
K FORWARD	*	*	*	(REF)	*	10S	10US	*	C-B E-B
C-B	E-B	E-B	*	K	K	*	(REF)	*	(REF)
(REF)	*	*	*	(REF)	*	C-B	E-B	*	*
2N3723B	1.30E+01	5.00E-02	4.18E-09	3.14E-09	1.01E-10	1.17E+00	1.30E-11	1.00E+00	1.00E+07
(1)	1.07E+00	6.48E-11	8.00E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+02	6.00E+00	2.10E+01
2N3723C	1.73E+01	1.07E+00	3.12E-09	3.77E-08	6.96E-12	1.19E+00	1.34E-11	8.00E-01	1.00E+07
(1)	1.06E+00	7.60E-11	8.00E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+02	6.00E+00	2.10E+01
2N3723D	1.13E+01	7.61E-01	3.03E-09	3.46E-08	4.17E-14	1.07E+00	7.76E-12	7.80E-01	1.00E+07
(1)	1.01E+00	1.65E-11	8.50E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+02	6.00E+00	2.10E+01
2N3723E	1.08E+01	7.17E-01	5.13E-09	3.17E-08	1.10E-10	1.19E+00	9.84E-12	8.00E-01	1.00E+07
(1)	1.12E+00	6.26E-11	8.00E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+02	6.00E+00	2.10E+01

TRANSISTOR DEVICE LIBRARY (Cont'd)

DEVICE NAME	HFF1	HFF1	TN	T1	I CS	MC	CCD	VCB1	RCL	IES
(TRAC FLAG)	4	4	---	+	---	+	---	+	---	---
ME	0	CEO	VEBT	REL	IPPC	IPPE	C-BBDV	E-BBDV	SURGE ZC	SURGE ZE
BULK RESISTANCE	0	2	SURGE C-B	0	7	SURGE E-B	0	DAMAGE K ((50NS))	DAMAGE K ((50NS))	DAMAGE K ((50NS))
(-B) (REF)	E-B	0	IUS	10US	10US	10US	C-B	E-B	C-B	E-B
K FORWARD	0	0	(REF)	---	---	(REF)	(REF)	(REF)	(REF)	(REF)
(-B) (REF)	E-B	0	C-B	K	K	K	K	K	K	K
(REF)	0	(REF)	0	E-B	C-B	(REF)	E-B	(REF)	(REF)	(REF)
283723F	1.34E+01	7.76E-01	3.24E-09	2.81E-08	5.71E-12	1.14E+00	9.62E-12	8.00E-01	1.00E+07	3.22E-13
(1)	1.01E+00	6.04E-11	8.00E-01	1.00E-07	1.00E-03	1.00E-05	1.00E+02	6.00E+00	2.10E+01	2.10E+01
283828	2.40E+01	2.10E+00	2.88E-08	4.06E-08	1.40E-13	1.02E+00	6.80E-12	7.50E-01	1.00E+07	3.10E-14
(1)	1.02E+00	1.80E-11	8.00E-01	1.00E+07	1.00E-03	1.00E-05	4.00E+01	3.00E+00	2.10E+01	2.10E+01
283866	1.00E+00	1.00E-01	8.10E-10	1.61E-08	1.39E-13	9.80E-01	5.70E-11	8.00E-01	1.00E+07	1.26E-13
(1)	1.05E+00	1.03E-10	8.50E-01	1.00E+07	1.00E-03	1.00E-05	5.50E+01	3.50E+00	2.10E+01	2.10E+01
283866A	8.50E+00	2.30E+00	8.86E-10	4.74E-08	1.02E-14	1.06E+00	7.56E-12	8.20E-01	1.00E+07	5.59E-15
(1)	1.04E+00	1.42E-11	8.60E-01	1.00E+07	1.00E-03	1.00E-05	5.50E+01	3.50E+00	2.10E+01	2.10E+01

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 28

DEVICE NAME	HFEI	HFEI	TN	TL	I CS	MC	CCD	VCB1	RCL	IES
(TRAC FLAG)	*	*	*	*	*	*	*	*	*	*
ME	*	*	*	*	*	*	*	*	*	*
CEO	*	*	*	*	*	*	*	*	*	*
BULK RESISTANCE	*	*	*	*	*	*	*	*	*	*
C-B	(REF)	E-B	IUS	IUS	SURGE E-B	SURGE E-B	DAMAGE K (<50NS)	DAMAGE K (>50NS)	D-B	E-B
K FORWARD	*	*	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)
C-B	(REF)	E-B	C-B	K	E-B	K	E-B	E-B	(REF)	(REF)
2N3866E	*	5.20E+00	*	2.00E+00	1.31E-09	4.17E-08	1.65E-14	1.06E+00	8.06E-12	1.00E+07
(1)	*	1.05E+00	*	1.56E-11	8.60E-01	1.00E+07	1.00E-03	1.00E-05	5.50E-01	3.50E+00
2N3866C	*	6.60E+00	*	2.41E+00	1.22E-09	2.73E-08	6.37E-13	1.31E+00	7.36E-12	7.80E-01
(1)	*	1.04E+00	*	1.51E-11	8.60E-01	1.00E+07	1.00E-03	1.00E-05	5.50E+01	3.50E+00
2N3866D	*	7.10E+00	*	3.40E+00	8.77E-10	4.36E-08	2.33E-14	1.07E+00	7.76E-12	7.80E-01
(1)	*	1.01E+00	*	1.65E-11	8.50E-01	1.00E+07	1.00E-03	1.00E-05	5.50E+01	3.50E+00
2N3866E	*	8.30E+00	*	5.00E+00	8.70E-10	1.69E-08	9.60E-15	3.06E+00	8.05E-12	1.00E+07
(1)	*	9.90E-01	*	1.74E-11	8.50E-01	1.00E+07	1.00E-03	1.00E-05	5.50E+01	3.50E+00

TRANSISTOR DEVICE LIBRARY (Cont'd)

TRANSISTOR DEVICE LIBRARY (Cont'd)

21

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 33																						
DEVICE NAME	HFFN	HFE1	TN	T1	T(S)	MC	CCU	VCBI	RCL	IES	SURGE ZC	SURGE ZE	DAMAGE K (>SONS)	C-B	E-B							
(TRAC FLAG)	*	*	+	---	*	---	*	+	+	+	---	+	---	+	---							
ME	*	*	CEO	*	REL	*	IPPC	*	IPPE	*	E-BBDY	*	SURGE ZC	*	SURGE ZE							
BULK RESISTANCE	*	*	1US	SURGE C-B	*	10US	*	Z SURGE E-B	*	DAMAGE K (<SONS)	*	DAMAGE K (>SONS)	*	DAMAGE K (>SONS)								
(C-B)	*	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)							
K FORWARD	*	*	*	*	K	*	*	*	*	*	*	*	*	*	*							
(C-B)	*	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)	*	(REF)							
2N4251F	*	1.79E+02	*	1.90E+01	*	5.17E-11	*	3.61E-09	*	4.53E-14	*	1.07E+00	*	3.52E-12	*	8.00E-01	*	1.00E+07	*	3.82E-14	*	3.82E-14
(1)	*	1.07E+00	*	4.53E-12	*	9.00E-01	*	1.00E+07	*	1.00E-03	*	1.00E-05	*	1.50E+01	*	4.50E+00	*	2.10E+01	*	2.10E+01	*	2.10E+01
2N4251F	*	2.12E+02	*	2.07E+01	*	4.88E-11	*	3.43E-09	*	5.66E-14	*	1.08E+00	*	3.58E-12	*	8.00E-01	*	1.00E+07	*	1.61E-14	*	1.61E-14
(1)	*	1.02E+00	*	4.80E-12	*	1.00E+00	*	1.00E+07	*	1.00E-03	*	1.00E-05	*	1.50E+01	*	4.50E+00	*	2.10E+01	*	2.10E+01	*	2.10E+01
2N4251F	*	2.12E+02	*	2.07E+01	*	4.88E-11	*	3.43E-09	*	5.66E-14	*	1.08E+00	*	3.58E-12	*	8.00E-01	*	1.00E+07	*	1.61E-14	*	1.61E-14
(0)	*	1.02E+00	*	4.80E-12	*	1.00E+00	*	1.00E+07	*	1.00E-03	*	1.00E-05	*	1.50E+01	*	4.50E+00	*	2.10E+01	*	2.10E+01	*	2.10E+01
5.60E-01	*	1.84E+00	*	9.75E+02	*	9.75E+02	*	(34)	*	9.78E+02	*	9.25E-05	*	6.51E-05	*	1.90E-01	*	2.91E-01	*	9.74E+02	*	9.74E+02
1.30E-02	*	3.20E-03	*	{ 60)	*	(60)	*	(34)	*	(60)	*	(60)	*	(60)	*	(60)	*	(60)	*	(60)	*	(60)
2N4517	*	1.00E-03	*	1.00E-05	*	6.00E+01	*	2.00E+01	*	2.10E+01	*	2.10E+01	*	5.00E-01	*	1.00E+07	*	5.00E-09	*	5.00E-09	*	5.00E-09
(0)	*	9.94E-01	*	1.41E-10	*	5.00E-01	*	1.00E+07	*	1.00E+01	*	5.00E+00	*	3.70E-07	*	1.59E-06	*	5.00E-09	*	9.94E-01	*	9.94E-01

DEVICE NAME	IFEN	FEEL	TN	TI	I CS	MC	CCU	VCB1	RCL	IES
(TRAC FLAG)	*	-----	*	-----	*	-----	*	-----	*	SURGE ZE
ME	*	CEO	*	REL	*	IPPC	*	E-BBDV	*	SURGE ZC
BULK RESISTANCE	*	-----	*	SURGE C-B	*	-----	*	DAMAGE K (<50NS)	*	DAMAGE K (>50NS)
C-B	(REF)	E-B	1US	10US	2	SURGE E-B	*	E-B	*	E-B
K FORWARD	*	-----	*	(REF)	*	1US	10US	(REF)	*	(REF)
C-B	(REF)	E-B	C-B	(REF)	E-B	*	K	*	K	K
2N4466X	*	*	*	*	*	*	*	*	*	
(C)	*	*	*	*	*	*	*	*	*	
1.30E+00	*	1.65E+00	*	6.BCE+02	2.41E+02	5.00E+02	2.80E+02	1.42E-04	6.33E-01	6.01E-0
(-34)	*	(34)	*	(34)	*	(34)	*	(60)	(60)	(60)
1.40E+02	*	2.7CE+03	*	6.U0	2.7CE+03	*	*	*	*	
2N501A1C	*	8.00E+01	*	2.00E+00	*	1.77E-10	*	3.18E-09	*	1.00E+07
(1)	*	1.22E+00	*	4.90E-12	*	8.62E-01	*	1.00E+07	*	1.14E+0
5.10E+00	*	6.40E+00	*	3.55E+02	*	4.70E+02	*	2.60E+02	*	6.20E+0
(-34)	*	(34)	*	(34)	*	(34)	*	(60)	(60)	(60)
3.90E+04	*	1.40E+04	*	6.U0	2.7CE+03	*	*	*	*	
2N5267	*	1.00E+01	*	9.00E+00	*	1.59E+00	*	7.96E+00	*	4.24E+12
(1)	*	9.94E+01	*	7.07E+12	*	5.00E+01	*	1.00E+01	*	5.00E+01
6.65E+00	*	1.65E+00	*	6.225E+02	*	1.50E+03	*	4.50E+01	*	2.10E+01
(-34)	*	(34)	*	(34)	*	(34)	*	(60)	(60)	(60)
3.70E+05	*	1.40E+05	*	6.U0	2.7CE+03	*	*	*	*	
2N5267	*	*	*	*	*	*	*	*	*	
(C)	*	*	*	*	*	*	*	*	*	
6.65E+00	*	1.65E+00	*	6.225E+02	*	1.50E+03	*	4.50E+01	*	2.10E+01
(-34)	*	(34)	*	(34)	*	(34)	*	(60)	(60)	(60)
3.70E+05	*	1.40E+05	*	6.U0	2.7CE+03	*	*	*	*	

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 35

DEVICE NAME	HFE1	IN	11	1CS	MC	CCD	VCBI	RCL	IES	
(TYP. FLAG)	*	*	*	*	*	*	*	*	*	
WF	*	CEC	*	REL	IPPC	C-BBDY	E-BBDY	SURGE ZC	SURGE ZE	
BULK RESISTANCE	*	*	*	*	*	*	*	*	*	
(C-E) E-B	*	SURGE C-B	*	SURGE E-B	*	DAMAGE K (SONS)	DAMAGE K (SONS)	*	*	
(S-E) E-B	*	1US	10US	10US	10US	E-B	E-B	C-B	E-B	
(S-E) E-B	*	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	
K	*	*	*	*	*	*	*	*	*	
C-B	*	E-B	E-B	E-B	E-B	K	K	K	K	
(S-E) E-B	*	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	
2N548	2.50E+01	1.50E+01	2.84E+00	3.18E-07	1.80E-08	9.94E-01	2.83E-11	5.00E-01	1.00E+07	1.80E-08
(1)	9.94E-11	2.83E-11	5.00E-01	1.00E+07	1.00E-03	1.00E-05	3.50E+01	3.00E+01	2.10E+01	1.60E+02
2N549	2.50E+01	1.00E+00	6.00E+02	6.30E+02	(32)	(32)	4.30E+02	3.00E+01	6.00E+02	4.30E+02
(1)	9.94E-11	7.07E-12	5.00E+01	1.00E+07	1.00E-03	1.00E-05	3.50E+01	3.00E+01	2.10E+01	2.10E+01
2N600	1.00E+01	9.00E+00	1.59E+09	7.96E-09	6.00E-09	9.94E-01	4.54E-12	5.00E-01	1.00E+07	6.00E-09
(1)	9.94E-01	7.07E-12	5.00E+01	1.00E+07	1.00E-03	1.00E-05	3.50E+01	3.00E+01	6.00E+02	4.30E+02
2N607	1.00E+01	9.00E+00	1.59E+09	7.96E-09	6.00E-09	9.94E-01	4.54E-12	5.00E-01	1.00E+07	6.00E-09
(1)	9.94E-01	7.07E-12	5.00E+01	1.00E+07	1.00E-03	1.00E-05	3.50E+01	3.00E+01	6.00E+02	4.30E+02
2N645	1.00E+01	9.00E+00	2.65E+09	1.59E+08	7.99E-10	9.94E-01	7.07E-12	5.00E-01	1.00E+07	7.99E-10
(1)	9.94E-01	7.07E-12	5.00E+01	1.00E+07	1.00E-03	1.00E-05	6.00E+01	5.00E+10	2.10E+01	2.10E+01

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 36

DEVICE NAME	HFE1	TN	TI	I _C S	MC	CCD	VCB1	RCL	IES
(TRAC FLAG)	*	*	*	*	*	*	*	*	*
WE	*	*	*	*	*	*	*	*	*
CEO	*	*	*	*	*	*	*	*	*
BULK RESISTANCE	*	*	*	*	*	*	*	*	*
C-BULK E-B	*	*	*	*	*	*	*	*	*
C-B (REF)	*	*	*	*	*	*	*	*	*
K FORWARD	*	*	*	*	*	*	*	*	*
C-B E-B	*	*	*	*	*	*	*	*	*
C-B (REF)	*	*	*	*	*	*	*	*	*
24457	0 1.00E+01	0 9.00E+00	0 1.27E-07	0 1.59E-06	0 6.98E-15	0 9.94E-01	0 2.47E-10	0 5.00E-01	0 1.00E+07
(C)	0 9.94E-01	0 2.67E-10	0 5.00E-01	0 1.00E+07	0 1.00E-03	0 1.00E-05	0 1.00E+02	0 8.00E+00	0 3.20E+00
(1)	0 9.94E-01	0 7.07E-11	0 5.00E-01	0 1.00E-07	0 1.00E-03	0 1.00E-05	0 1.00E+01	0 5.00E+00	0 2.10E+01
24696	0 2.00E+01	0 5.00E+00	0 1.59E-09	0 1.77E-09	0 4.00E-17	0 9.94E-01	0 4.95E-11	0 5.00E-01	0 1.00E+07
(1)	0 9.94E-01	0 7.07E-11	0 5.00E-01	0 1.00E-07	0 1.00E-03	0 1.00E-05	0 6.00E+01	0 5.00E+00	0 2.10E+01
24697	0 2.00E+01	0 5.00E+00	0 1.59E-09	0 1.77E-09	0 4.00E-17	0 9.94E-01	0 4.95E-11	0 5.00E-01	0 1.00E+07
(1)	0 9.94E-01	0 7.07E-11	0 5.00E-01	0 1.00E+07	0 1.00E-03	0 1.00E-05	0 6.00E+01	0 5.00E+00	0 2.10E+01
24705	0 2.50E+01	0 5.00E+00	0 1.06E-09	0 6.39E-12	0 1.00E-07	0 1.00E-08	0 1.83E+00	0 1.37E-11	0 3.00E-01
(C)	0 1.63E+00	0 6.39E-12	0 3.00E-01	0 1.00E-07	0 1.00E-03	0 1.00E-05	0 1.50E+01	0 3.50E+00	0 7.25E+01
24706	0 4.50E-01	0 2.20E+00	0 1.50E+02	0 3.60E+02	0 3.60E+02	0 3.60E+02	0 (34)	0 3.18E-06	0 1.13E-06
24707	0 7.90E-05	0 3.60E-05	0	0	0	0	0 (60)	0	0

TRANSISTOR DEVICE LIBRARY (Cont'd)

TRANSISTOR DEVICE LIBRARY (Cont'd)

TRANSISTOR DEVICE LIBRARY (Cont'd)

DEVICE NAME	HFE1	TN	T1	IC5	MC	CCD	VGB1	RCL	LES
(TAC FLAG)	*	-	-	-	-	-	-	-	-
ME	*	CEO	VER1	REL	IPPC	IPPE	C-BBDY	SURGE ZC	SURGE ZE
BULK RESISTANCE	*	-	-	-	-	-	-	-	-
C-B (REF)	E-B	LUS	SURGE C-B	E-B	L SURGE	E-B	DAMAGE K (<50NS)	DAMAGE K	DAMAGE K
K FORWARD	*	-	-	-	-	-	10US (REF)	E-B	C-B
C-B (REF)	E-B	C-B	E-B	C-B	K	K	(REF)	*9EF	E-B
(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	(REF)	K
2N814	2.60E+01	1.10E-01	3.66E-10	1.19E-08	2.62E-13	1.05E+00	4.70E-12	9.00E-01	1.00E+07
(1)	9.92E-01	5.90E-12	8.00E-01	1.00E+07	1.00E-03	1.00E-05	4.00E+01	5.00E+00	2.10E+01
2N916	1.07E+02	3.30E-01	5.15E-10	4.46E-07	3.75E-11	1.43E+00	4.60E-12	8.00E-01	1.00E+07
(1)	9.68E-01	7.10E-12	9.00E-01	1.00E+07	1.00E-03	1.00E-05	7.00E+01	5.00E+00	2.10E+01
2N916	2.16E+01	3.50E-01	5.05E-10	3.89E-07	1.93E-13	1.11E+00	6.70E-12	9.00E-01	1.00E+07
(1)	9.92E-01	7.30E-12	9.00E-01	1.00E+07	1.00E-03	1.00E-05	4.50E+01	5.00E+00	2.10E+01
2N916	4.39E+01	1.00E+00	1.76E-11	2.25E-08	3.20E-15	1.02E+00	2.40E-12	1.00E+00	1.00E+07
(1)	1.025E+00	1.00E-12	1.00E+00	1.00E+07	1.00E-03	1.00E-05	3.00E+01	3.00E+00	2.10E+01

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 41

DEVICE NAME	HFE1	TN	T1	I _C	MC	CCD	V _{CB1}	RCL	IES
(TKAC FLAG)	*	*	*	*	*	*	*	*	*
ME	*	CEO	*	KEL	*	IPPE	*	F-BBDY	SURGE IC
BULK RESISTANCE	*	*	*	*	*	*	*	*	SURGE ZF
C-B (REF)	*	IUS	Z SOURCE C-B	IUS	SURGE E-B	DAMAGE K (<SONS)	*	*	*
K FORWARD	*	(REF)	*	(REF)	10US	E-B	C-B	E-B	DAMAGE K (>SONS)
C-B (REF)	*	*	*	*	(REF)	(REF)	(REF)	(REF)	E-B
2N30	3.40E+01	*	1.00E-01	9.03E-10	* 5.00E-08	* 1.20E-13	* 1.05E+00	* 5.00E-12	* 8.00E-01
(1)	9.92E-01	*	7.20E-12	9.00E-01	* 1.00E+07	* 1.00E-03	* 1.00E-05	* 4.50E+01	* 5.00E+00
2N55A	1.66E+02	*	4.00E-01	8.95E-11	* 4.29E-09	* 8.05E-06	* 1.06E+00	* 6.00E-12	* 4.00E-01
(1)	1.05E+00	*	4.30E-12	5.00E-01	* 1.00E+07	* 1.00E-03	* 1.00E-05	* 6.00E+01	* 5.00E+00
2N464	1.04E+02	*	1.00E+00	4.26E-10	* 5.50E-09	* 1.44E-06	* 1.08E+00	* 3.20E-12	* 5.00E-01
(1)	1.08E+00	*	2.50E-12	5.00E-01	* 1.00E+07	* 1.00E-03	* 1.00E-05	* 1.50E+01	* 2.50E+00
2N4726A	1.79E+02	*	1.77E+00	2.19E-10	* 1.34E-08	* 1.72E+00	* 1.22E+00	* 9.93E-12	* 7.50E-01
(1)	1.03E+00	*	8.83E-12	8.00E-01	* 1.00E+07	* 1.00E-03	* 1.00E-05	* 1.00E+01	* 2.10E+01

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 62

DEVICE NAME	HFEN	HFEI	TN	T1	TCS	MC	CCC	VGB1	RCL	LES
(TRAC FLAG)	*	*	*	*	*	*	*	*	*	*
2N9726B	1.23E+02	1.37E+00	2.48E-10	1.39E-07	3.63E-12	1.27E+00	9.81E-12	7.50E-01	1.00E+07	8.07E-14
(1)	1.06E+00	8.72E-12	6.00E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+01	2.10E+01	2.10E+0	2.10E+0
2N9726C	1.38E+02	2.02E+00	2.48E-10	1.34E-07	8.07E-12	1.33E+00	9.35E-12	7.50E-01	1.00E+07	4.23E-11
(1)	1.21E+00	6.72E-12	8.00E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+01	2.10E+01	2.10E+0	2.10E+0
2N9726F	1.75E+02	1.50E-02	1.99E-10	2.96E-09	1.69E-11	1.14E+00	1.01E-11	8.00E-01	1.00E+07	2.21E-1
(1)	9.75E-01	8.33E-12	9.00E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+01	2.10E+01	2.10E+0	2.10E+0
2N9726F	9.88E+01	1.78E+00	3.86E-10	1.15E-07	1.14E+00	9.84E-12	8.00E-01	1.00E+07	2.53E-1	-----
(1)	1.01E+00	8.64E-12	9.00E-01	1.00E+07	1.00E-03	1.00E-05	1.00E+01	2.10E+01	2.10E+0	2.10E+0

TRANSISTOR DEVICE LIBRARY (Cont'd)

PAGE 43

DEVICE NAME	HFE1	*	TN	*	TI	*	ICS	*	MC	*	CCD	*	VCB1	*	RCL	*	IES			
(TRAC FLAG)	*	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -			
ME	*	CEU	*	VEBI	*	REL	*	IPPC	*	IPPE	*	C-BBDY	*	E-BBDY	*	SURGE ZC	*	SURGE ZE		
BULK RESISTANCE	*	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -				
C-B	E-B	*	LUS	*	SURGE C-B	*	Z SURGE E-B	*	DAMAGE K (<SONS)	*	DAMAGE K (>SONS)	*	E-B	*	C-B	*	E-B			
(REF)	*	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -				
K FORWARD	*	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -				
C-B	(REF)	*	C-B	*	E-B	*	C-B	*	K	*	K	*	K	*	K	*	K			
(REF)	*	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -	+	- - - -				
24976	*	8.00E+01	*	2.00E+00	*	1.77E-10	*	3.18E-09	*	1.10E-06	*	1.22E+00	*	2.69E-12	*	6.65E-01	*	1.00E+07	*	1.14E-06
(1)	*	1.22E+00	*	4.90E-12	*	8.62E-01	*	1.00E+07	*	1.00E-03	*	1.00E-05	*	1.50E+01	*	2.00E+00	*	2.10E+01	*	2.10E+01
*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	
*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	
*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	

END OF LISTING

TABLE III. DEVICE PARAMETER REFERENCES

<u>CODE</u>	<u>REPORT</u>
001	Preliminary Report--Semiconductor Damage Study, Braddock, Dunn, & McDonald (23 December 1968).
002	D. C. Wunsch and L. Marzetteli, BDM Final Report Volume 1, Semiconductor and Non-Semiconductor Damage Study, Braddock, Dunn, & McDonald 375-69-F-0168 (April 1969).
003	J. B. Singletary and D. C. Wunsch, Final Report on Semiconductor Damage Study Phase II, Braddock, Dunn, & McDonald/A-6670-TR (June 1970).
004	Braddock, Dunn, & McDonald, Final Summary Report on Semiconductor Damage Study Phase II, BDM/A-84-70-TR (February 1971).
005	D. C. Wunsch et al, Semiconductor Vulnerability Phase II Report, Theoretical Estimates of Failure Levels of Selected Semiconductor Diodes & Transistors, AFWL-TR-73-119, Vol 1 (July 1973).
006	D. C. Wunsch, R. L. Cline, and G. R. Case, Semiconductor Vulnerability Phase II Report, Braddock, Dunn, & McDonald/A-42-69-R (December 1969).
007	J. B. Singletary, W. O. Collier, and J. A. Meyers, Semiconductor Vulnerability Phase III Report, Braddock, Dunn, & McDonald/A-75-70-TR (August 1970).
010	D. L. Durgin et al, Methods, Devices, and Circuits for the EMP Hardening of Army Electronics, ECOM-0275-F, Braddock, Dunn, & McDonald/A-119-72-TR (July 1972).
011	Boeing Aerospace Company and Braddock, Dunn, & McDonald, EMP Susceptibility of Semiconductor Components, Boeing, Braddock, Dunn, & McDonald/A-110-74-TR (September 1974).
012	Braddock, Dunn, & McDonald and Boeing Co., Addendum to EMP Susceptibility of Semiconductor Components, D224-13042-2 (July 1975).
013	Braddock, Dunn, & McDonald and Boeing Co., Electromagnetic Susceptibility of Semiconductor Components, Final Report (September 1975).

TABLE III. DEVICE PARAMETER REFERENCES (Cont'd)

<u>CODE</u>	<u>REPORT</u>
014	G. Brown et al, Experimental Damage Constant Summary--Braddock, Dunn, & McDonald/A-99-74-TR-R1 (20 September 1974).
015	Diode and SCR--D.A.T.A. Book, Derivation and Tabulation Associates, Inc. (1970).
016	Transistor--D.A.T.A. Book, Derivation and Tabulation Associates, Inc. (1969).
017	SAP-1 Computer Listing. Data as reported in DASA Handbook (1972).
020	Experimental data from DASA EMP Handbook. DASA 2114-1 (September 1968).
021	Estimated data from DASA EMP Handbook. DASA 2114-1 (September 1968).
022	Calculated as per Section III of DNA EMP Handbook (1972).
023	DNA EMP Handbook (September 1975).
024	Joe Miletta, EMP Effects on Components, internal memo, Harry Diamond Laboratories.
025	Joe Miletta, LANCE System Component Damage Characterizations, internal memo, Harry Diamond Laboratories.
026	D. M. Tasca, Submicrosecond Pulse Power Failure Modes in Semiconductor Devices, General Electric Company, Re-Entry & Environmental Systems Division, Document No. 70SD401 (January 1970).
027	D. M. Tasca, Energy-Time Dependence of Second Breakdown in Semiconductors for Submicrosecond Electrical Pulses, General Electric Company, Missile and Space Division, Document No. 67SD7253 (October 1967).
030	D. M. Tasca, J. Peden, and J. Andrews, Theoretical and Experimental Studies of Semiconductor Device Degradation due to high Power Electrical Transients, GE Document No. 73SD4289 (December 1973).
031	Bruno Kalab, Analysis of Failure of Electronic Circuits from EMP-Induced Signals, Harry Diamond Laboratories TR-1615 (August 1973).

TABLE III. DEVICE PARAMETER REFERENCES (Cont'd)

<u>CODE</u>	<u>REPORT</u>
032	G. Baker, EMP Vulnerability Analysis of M-109, M-110 Self-Propelled Howitzers, Harry Diamond Laboratories TR-1797, to be published.
033	G. Baker, EMP Vulnerability Analysis of Radio Sets AN/PRC-77, AN/VRC-64 and AN/GRC-160 (U), Harry Diamond Laboratories TR-1747 (February 1976). (SECRET RESTRICTED DATA)
034	G. Gornak et al, EMP Assessment for Army Tactical Communications Systems: Transmission Systems, Series No. 1, Radio Terminal Set AN/TRC-145 (U), Harry Diamond Laboratories TR-1746 (February 1976). (SECRET RESTRICTED DATA)
035	See Ref 034.
050	J. D. Holder and V. Ruwe--Statistical Component Damage Study, U.S. Army Missile Command Report RG-TR-71-1 (January 1971).
051	Pete Stadler, Failure Threshold and Resistance of the Protected and Unprotected 2N2222 Transistor in the Short Pulse Width Regime, Philco-Ford Corp, U-4976 (May 1972).
052	EMP Electronic Design Handbook, Boeing Aerospace Corporation D224-10019-1 (April 1973).
053	C. R. Jenkins and J. A. Meyers, Integrated Circuits Test Program, Final Report, Word Order 2-14, Braddock, Dunn, & McDonald/A-98-73-TR (July 1973).
054	D. R. Alexander, T. J. Zwolinski, and C. R. Jenkins, Integrated Circuits and Discrete Semiconductor Components Test Program, Technical Directive 4-6, BDM Monthly Progress Reports (January, February, and March 1974).
055	J. S. Smith, Pulse Power Testing of Microcircuits, Rome Air Development Center TR-71-59 (October 1971).
056	The Boeing Company, Memorandum No. 2-6731-0000-C/S-102, Subject: Pulse Damage Data from Integrated Circuits and Electronic Parts (26 September 1973).
057	G. J. Rimbert et al, Resistor Modeling Program, BDM Final Report, ASV Work Order 2-14 [n.d.].
060	See Ref 034.

TABLE III. DEVICE PARAMETER REFERENCES (Cont'd)

<u>CODE</u>	<u>REPORT</u>
061	Data value from our previous data base at MERADCOM.
062	See Ref 034.
063	Forward biased damage constant from graph in DNA Handbook (1972).
064	Weighted average from Ref 013.
065	Averaged from Ref 013.
066	These data are from Ref 034, but conflicting values were obtained from Ref 025.
067	D. Tacsa, J. Peden, and D. Nepveux, Pulsed Power Failure Modes: Conference Proceedings, Component Degradation from Transient Inputs (April 1970).
070	Data derived by averaging the means of data in Ref 067.
071	Data from Ref 034 and 062.
777	UNKNOWN

APPENDIX A.--JCL FOR EXECUTING DAMTRAC AT HDL

The following is the JCL (job control language) necessary to execute DAMTRAC on the HDL IBM 370/168.

DAMTRAC

```
//JOBCARD
//stepname EXEC FORTPLG,PARM.LKED=LET, COND.GO=(8,LT),
//           PRELIB='library name'
//LKED.SYSIN DD *
INCLUDE SYSLIB(TRAC,BLKDAT)
ENTRY MAIN
//GO.FT06F001 DD SYSOUT=A,DCB=(RECFM=VA,LRECL=137,BLKSIZE=137)
//GO.FT07F001 DD DUMMY
//GO.FT01F001 DD UNIT=VIO,SPACE=(TRK,(1,1)),DISP=(NEW),DELETE
//GO.FT10F001 DD DSN=&&TEMP,UNIT=SYSDA,DISP=(NEW,DELETE),
//           DCB=(RECFM=FB,LRECL=80,BLKSIZE=80),SPACE=(80,(100,50))
//GO.FT11F001 DD DSN='diode library', DISP=SHR
//GO.FT12F001 DD DSN='transistor library',DISP=SHR
//GO.FT17F001 DD DUMMY
//GO.FT50F001 DD SYSOUT=A,DCB=(RECFM=FBA,LRECL=133,BLKSIZE=3990)
//GO.SYSIN   DD *
```

TRAC piece part data deck

/*

The following is the JCL necessary to execute DAMTRAC with a user-written TREAQ subroutine on the HDL IBM 370/168.

DAMTRAC JCL w/TREAQ

```
//JOBCARD
//stepname EXEC FORTPC
           user written TREAQ subroutine
/*
//stepname EXEC FORTPLG,PARM.LKED=LET,COND.GO=(8,LT),
           PRELIB='library name'
```

APPENDIX A

```
//LKED.SYSLIN DD DSN=&&LOADSET,DISP=(OLD,PASS)
//          DD DDNAME=SYSIN
//LKED.SYSIN  DD *
   INCLUDE SYSLIB(TRAC,BLKDATA)
 ENTRY MAIN
//GO.FT06F001 DD SYSOUT=A,DCB=(RECFM=VA,LRECL=137,BLKSIZE=137)
//GO.FT07F001 DD DUMMY
//GO.FT01F001 DD UNIT=VIO,SPACE=(TRK,(1,1)),DISP=(NEW,DELETE)
//GO.FT10F001 DD DSN=&&TEMP,UNIT=SYSDA,DISP=(NEW,DELETE),
//          DCB=(RECFM=FB,LRECL=80,BLKSIZE=80,SPACE=(80,(100,50))
//GO.FT11F001 DD DSN='diode library',DISP=SHR
//GO.FT12F001 DD DSN='transistor library', DISP=SHR
//GO.FT17F001 DD DUMMY
//GO.FT50F001 DD SYSOUT=A,DCB=(RECFM=FBA,LRECL=133,BLKSIZE=3990)
//GO.SYSIN    DD *
```

TRAC piece part data deck

/*

DISTRIBUTION

DEFENSE DOCUMENTATION CENTER
CAMERON STATION, BUILDING 5
ALEXANDRIA, VA 22314
ATTN DDC-TCA (12 COPIES)

COMMANDER
US ARMY MATERIEL DEVELOPMENT
& READINESS COMMAND
5001 EISENHOWER AVENUE
ALEXANDRIA, VA 22333
ATTN DRXAM-TL, HQ TECH LIBRARY
ATTN DRCRP/MG C. M. MCKEEN, JR.
ATTN DRCRP-M/COL R. W. SPECKER
ATTN DRCPM-SCM-WF
ATTN DRCDE-D/MR. HUNT
ATTN DRCDE-D/COL J. F. BLEECKER
ATTN DRCDE, DIR FOR DEV & ENGR
ATTN DRCDE-DE/H. DARRACOTT
ATTN DRCMS-I/DR. R. P. UHLIG
ATTN DRCMS-I/MR. E. O'DONNEL
ATTN DRCDMD-ST/N. L. KLEIN

COMMANDER
US ARMY ARMAMENT MATERIEL
READINESS COMMAND
ROCK ISLAND ARSENAL
ROCK ISLAND, IL 61201
ATTN DRSAR-ASF, FUZE & MUNITION DIV
ATTN DRSAR-PDM/J. A. BRINKMAN
ATTN DRCPM-VFF

COMMANDER
USA MISSILE & MUNITIONS
CENTER & SCHOOL
REDSTONE ARSENAL, AL 35809
ATTN ATSK-CTD-F

COMMANDING OFFICER
NAVAL TRAINING EQUIPMENT CENTER
ORLANDO, FL 32813
ATTN TECHNICAL LIBRARY

DEFENSE ADVANCED RESEARCH
PROJECTS AGENCY
1400 WILSON BLVD
ARLINGTON, VA 22209
ATTN TECH INFORMATION OFFICE
ATTN DIR, STRATEGIC TECHNOLOGY
ATTN DIR, TACTICAL TECHNOLOGY

DIRECTOR
DEFENSE COMMUNICATION ENG CENTER
1860 WIEHLE AVENUE
RESTON, VA 22090
ATTN R104, M. J. RAFFENSPERGER
ATTN R800, R. E. LYONS
ATTN R320, A. IZZO

DIRECTOR
DEFENSE INTELLIGENCE AGENCY
WASHINGTON, DC 20301
ATTN DI-2, WEAPONS & SYSTEMS DIV

DIRECTOR
DEFENSE NUCLEAR AGENCY
WASHINGTON, DC 20305
ATTN PETER HAAS, DEP DIR,
SCIENTIFIC TECHNOLOGY
ATTN RAEV, MAJ S. O. KENNEDY, SR.
ATTN VLIS, LTC ADAMS

DEPARTMENT OF DEFENSE
DIRECTOR OF DEFENSE RESEARCH & ENGINEERING
WASHINGTON, DC 20301
ATTN DEP DIR (TACTICAL WARFARE PROGRAMS)
ATTN DEP DIR (TEST & EVALUATION)
ATTN DEFENSE SCIENCE BOARD
ATTN ASST DIR SALT SUPPORT
GP/MR. J. BLAYLOCK

CHAIRMAN
JOINT CHIEFS OF STAFF
WASHINGTON, DC 20301
ATTN J-3, NUCLEAR WEAPONS BR
ATTN J-3, EXER PLANS & ANALYSIS DIV
ATTN J-5, NUCLEAR DIR NUCLEAR POLICY BR
ATTN J-5, REQUIREMENT & DEV BR
ATTN J-6, COMMUNICATIONS-ELECTRONICS

DEPARTMENT OF DEFENSE
JOINT CHIEFS OF STAFF
STUDIES ANALYSIS & GAMING AGENCY
WASHINGTON, DC 20301
ATTN STRATEGIC FORCES DIV
ATTN GEN PURPOSE FORCES DIV
ATTN TAC NUC BR
ATTN SYS SUPPORT BR

ASSISTANT SECRETARY OF DEFENSE
PROGRAM ANALYSIS AND EVALUATION
WASHINGTON, DC 20301
ATTN DEP ASST SECY (GEN PURPOSE PROG)
ATTN DEP ASST SECY (REGIONAL PROGRAMS)
ATTN DEP ASST SECY (RESOURCE ANALYSIS)

DEPARTMENT OF THE ARMY
OFFICE, SECRETARY OF THE ARMY
WASHINGTON, DC 20301
ATTN ASST SECRETARY OF THE ARMY (I&L)
ATTN DEP FOR MATERIEL ACQUISITION
ATTN ASST SECRETARY OF THE ARMY (R&D)

DEPARTMENT OF THE ARMY
ASSISTANT CHIEF OF STAFF FOR INTELLIGENCE
WASHINGTON, DC 20301
ATTN DAMI-OC/COL J. A. DODDS
ATTN DAMI-TA/COL F. M. GILBERT

US ARMY SECURITY AGENCY
ARLINGTON HALL STATION
4000 ARLINGTON BLVD
ARLINGTON, VA 22212
ATTN DEP CH OF STAFF RESEARCH
& DEVELOPMENT

DISTRIBUTION (Cont'd)

DEPARTMENT OF THE ARMY US ARMY CONCEPTS ANALYSIS AGENCY 8120 WOODMONT AVENUE BETHESDA, MD 20014 ATTN COMPUTER SUPPORT DIV ATTN WAR GAMING DIRECTORATE ATTN METHODOLOGY AND RESOURCES DIRECTORATE ATTN SYS INTEGRATION ANALYSIS DIRECTORATE ATTN JOINT AND STRATEGIC FORCES DIRECTORATE ATTN FORCE CONCEPTS AND DESIGN DIRECTORATE ATTN OPERATIONAL TEST AND EVALUATION AGENCY	COMMANDER US ARMY FOREIGN SCIENCE AND TECHNOLOGY CENTER 220 SEVENTH ST., NE CHARLOTTESVILLE, VA 22901
DIRECTOR NATIONAL SECURITY AGENCY FORT GEORGE G. MEADE, MD 20755	DIRECTOR US ARMY MATERIEL SYSTEMS ANALYSES ACTIVITY ABERDEEN PROVING GROUND, MD 21005 ATTN DRXSY-C/DON R. BARTHEL ATTN DRXSY-T/P. REID
COMMANDER-IN-CHIEF EUROPEAN COMMAND APO NEW YORK, NY 09128	COMMANDER US ARMY SATELLITE COMMUNICATIONS AGENCY FT. MONMOUTH, NJ 07703 ATTN LTC HOSMER
HEADQUARTERS US EUROPEAN COMMAND APO NEW YORK, NY 09055	DIRECTOR BALLISTIC RESEARCH LABORATORIES ABERDEEN PROVING GROUND, MD 21005 ATTN DRXBR-XA/MR. J. MESZAROS
DIRECTOR WEAPONS SYSTEMS EVALUATION GROUP OFFICE, SECRETARY OF DEFENSE 400 ARMY-NAVY DRIVE WASHINGTON, DC 20305 ATTN DIR, LT GEN GLENN A. KENT	COMMANDER US ARMY AVIATION SYSTEMS COMMAND 12TH AND SPRUCE STREETS ST. LOUIS, MO 63160 ATTN DRCPM-AAH/ROBERT HUBBARD
DEPARTMENT OF THE ARMY DEPUTY CHIEF OF STAFF FOR OPERATIONS & PLANS WASHINGTON, DC 20301 ATTN DAMO-RQD/COL E. W. SHARP ATTN DAMO-SSP/COL D. K. LYON ATTN DAMO-SSN/LTC R. E. LEARD ATTN DAMO-SSN/LTC B. C. ROBINSON ATTN DAMO-RQZ/COL G. A. POLLIN, JR. ATTN DAMO-TCZ/MG T. M. RIENZI ATTN DAMO-ZD/A. GOLUB ATTN DAMO-RQA/COL M. T. SPEIR	DIRECTOR EUSTIS DIRECTORATE US ARMY AIR MOBILITY R&D LABORATORY FORT EUSTIS, VA 23604 ATTN SAVDL-EU-MOS/MR. S. POCLUYKO ATTN SAVDL-EU-TAS (TETRACORE)
DEPARTMENT OF THE ARMY CHIEF OF RESEARCH DEVELOPMENT AND ACQUISITION OFFICE WASHINGTON, DC 20301 ATTN DAMA-RAZ-A/R. J. TRAINOR ATTN DAMA-CSM-N/LTC OGDEN ATTN DAMA-WSA/COL W. E. CROUCH, JR. ATTN DAMA-WSW/COL L. R. BAUMANN ATTN DAMA-CSC/COL H. C. JELINEK ATTN DAMA-CSM/COL H. R. BAILEY ATTN DAMA-WSZ-A/MG D. R. KEITH ATTN DAMA-WSM/COL J. B. OBLINGER, JR. ATTN DAMA-PPR/COL D. E. KENNEY	COMMANDER 2D BDE, 101ST ABN DIV (AASLT) FORT CAMPBELL, KY 42223 ATTN AFZB-KB-SO ATTN DIV SIGNAL OFFICER, AFBZ-SO/MAJ MASON
COMMANDER BALLISTIC MISSILE DEFENSE SYSTEMS P.O. BOX 1500 HUNTSVILLE, AL 35807 ATTN BMDSC-TEN/MR. JOHN VEFNEMAN	COMMANDER US ARMY ELECTRONICS COMMAND FT. MONMOUTH, NJ 07703 ATTN PM, ATACS/DRCPM-ATC/LTC DOBBINS ATTN DRCPM-ATC-TM ATTN PM, ARTADS/DRCPM-TDS/ BG A. CRAWFORD ATTN DRCPM-TDS-TF/COL D. EMERSON ATTN DRCPM-TDS-TO ATTN DRCPM-TDS-FB/LTC A. KIRKPATRICK ATTN PM, MALOR/DRCPM-MALR/COL W. HARRISON ATTN PM, NAVCOM/DRCPM-NC/ COL C. McDOWELL, JR. ATTN PM, REMBASS/DRCPM-RBS/ COL R. COTTEY, SR. ATTN DRSEL-TL-IR/MR. R. FREIBERG ATTN DRSEL-SA/NORMAN MILLSTEIN ATTN DRSEL-MA-C/J. REAVIS ATTN DRSEL-CE-ES/J. A. ALLEN

DISTRIBUTION (Cont'd)

COMMANDER US ARMY MISSILE MATERIEL READINESS COMMAND REDSTONE ARSENAL, AL 35809 ATTN DRSMI-FRR/DR. F. GIPSON ATTN DRCPM-HA/COL P. RODDY ATTN DRCPM-LCCX/L. B. SEGHEL (LANCE) ATTN DRCPM-MD/GENE ASHLEY (SAM-D) ATTN DRCPM-MP ATTN DRCPM-PE/COL SKEMP (PERSHING) ATTN DRCPM-SHO ATTN DRCPM-TO ATTN DRSMI-R, RDE + MSL DIRECTORATE	PROJECT MANAGER MOBILE ELECTRIC POWER 7500 BACKLICK ROAD SPRINGFIELD, VA 22150 ATTN DRCPM-MEP
COMMANDER US ARMY MATERIEL DEV & READINESS COMMAND PICATINNY ARSENAL DOVER NJ 07801 ATTN DRDAR-ND-V/DANIEL WAXLER	DEPUTY COMMANDER US ARMY NUCLEAR AGENCY 7500 BACKLICK RD BUILDING 2073 SPRINGFIELD, VA 22150 ATTN MONA-WE/COL A. DEVERILL
COMMANDER US ARMY TANK/AUTOMOTIVE MATERIEL READINESS COMMAND WARREN, MI 48090 ATTN DRSI-RHT/MR. P. HASEK ATTN DRCPM(XM-L)/MR. L. WOOLCOT ATTN DRCPM-GCM-SW/MR. R. SLAUGHTER	COMMANDER US ARMY SIGNAL SCHOOL FT. GORDON, GA 30905 ATTN AISO-CID/BILL MANNELL ATTN ATST-CTD-CS/CAPT G. ALEXANDER (INTACS) ATTN ATSO-CID-CS/MR. TAYLOR ATTN ATSN-CD-OR/MAJ CARR
PRESIDENT DA, HA, US ARMY ARMOR AND ENGINEER BOARD FORT KNOX, KY 40121 ATTN STEBB-MO/MAJ SANZOTERRA	DIRECTOR JOINT TACTICAL COMMUNICATIONS OFFICE PT. MONMOUTH, NJ 07703 ATTN TRI-TAC/NORM BECHTOLD
COMMANDER WHITE SANDS MISSILE RANGE WHITE SANDS MISSILE RANGE, NM 88002 ATTN STEWS-TE-NT/MARVIN SQUIRES	COMMANDER US ARMY COMMAND AND GENERAL STAFF COLLEGE FORT LEAVENWORTH, KS 66027
COMMANDER TRASANA SYSTEM ANALYSIS ACTIVITY WHITE SANDS, NM 88002 ATTN ATAA-TDO/DR. D. COLLIER	COMMANDER US ARMY COMBAT DEVELOPMENTS EXPERIMENTATION COMMAND FORT ORD, CA 93941
COMMANDER 197TH INFANTRY BRIGADE FORT BENNING, GA 31905 ATTN COL WASIAK	COMMANDER HQ MASSTER FORT HOOD, TX 76544
COMMANDER US ARMY COMMUNICATIONS COMMAND FORT HUACHUCA, AZ 85613 ATTN ACC-AD-C/H. LASITTER (EMP STUDY GP)	COMMANDER US ARMY AIR DEFENSE SCHOOL FORT BLISS, TX 79916 ATTN ATSA-CD
COMMANDER USA COMBINED ARMS COMBAT DEVELOPMENTS ACTIVITY FT. LEAVENWORTH, KS 66027 ATTN ATCAC ATTN ATCACO-SD/LTC L. PACHA ATTN ATCA/CO/COL HUBBERT ATTN ATCA-CCM-F/LTC BECKER ATTN ATSW-TD-3 NUCLEAR STUDY TEAM/LT D. WILKINS	COMMANDER US ARMY ARMOR SCHOOL FORT KNOX, KY 40121 ATTN ATSB-CTD (2 COPIES)
	COMMANDER US ARMY AVIATION CENTER FORT RUCKER, AL 36360 ATTN ATST-D-MS (2 COPIES)
	COMMANDER US ARMY ORDNANCE CENTER AND SCHOOL ABERDEEN PROVING GROUND, MD 21005 ATTN USAOC&S ATTN ATSL-CTD
	COMMANDER US ARMY SIGNAL SCHOOL FT. GORDON, GA 30905 ATTN ATSS-CTD (2 COPIES)

DISTRIBUTION (Cont'd)

COMMANDER US ARMY ENGINEER SCHOOL FORT BELVOIR, VA 22060 ATTN ATSE-CTD (2 COPIES)	COMMANDER AF WEAPONS LABORATORY, AFSC KIRTLAND AFB, NM 87117 ATTN ES, ELECTRONICS DIVISION ATTN EL, J. DARRAH ATTN TECHNICAL LIBARY ATTN D. I. LAWRY
COMMANDER US ARMY INFANTRY SCHOOL FORT BENNING, GA 31905 ATTN ATSH-CTD (2 COPIES)	COMMANDER AERONAUTICAL SYSTEMS DIVISION, AFSC WRIGHT-PATTERSON AFB, OH 45433 ATTN ASD/YH, DEPUTY FOR B-1
COMMANDER US ARMY INTELLIGENCE CENTER AND SCHOOL FORT HUACHUCA, AZ 85613 ATTN ATSI-CTD (2 COPIES)	COMMANDER HQ SPACE AND MISSILE SYSTEMS ORGANIZATION P.O. 96960 WORLDWAYS POSTAL CENTER LOS ANGELES, CA 90009 ATTN S7H, DEFENSE SYSTEMS APL SPO ATTN XRT, STRATEGIC SYSTEMS DIV ATTN SYS, SURVIVABILITY OFC
COMMANDER US ARMY FIELD ARTILLERY SCHOOL FORT SILL, OK 73503 ATTN ATSF-CTD (2 COPIES)	SPACE AND MISSILE SYSTEMS ORGANIZATION NORTON AFB, CA 92409 ATTN MMH, HARD ROCK SILO DEVELOPMENT
CHIEF OF NAVAL OPERATIONS NAVY DEPARTMENT WASHINGTON, DC 20350 ATTN NOP-932, SYS EFFECTIVENESS DIV CAPT E. V. LANEY ATTN NOP-9860, COMMUNICATIONS BR COR L. LAYMAN ATTN NOP-351, SURFACE WEAPONS BR CAPT G. A. MITCHELL ATTN NOP-622C, ASST FOR NUCLEAR VULNERABILITY, R. PIACESI	COMMANDER AF SPECIAL WEAPONS CENTER, AFSC KIRTLAND AFB, NM 87117
COMMANDER NAVAL ELECTRONICS SYSTEMS COMMAND, HQ 2511 JEFFERSON DAVIS HIGHWAY ARLINGTON, VA 20360 ATTN PME-117-21, SANGUINE DIV	ASSISTANT CHIEF OF STAFF FOR COMMUNICATIONS ELECTRONICS XVIII AIRBORNE CORPS FORT BRAGG, NC 28307 ATTN AFZA-CE/LTC K. KILLINGSTEAD
HEADQUARTERS, NAVAL MATERIEL COMMAND STRATEGIC SYSTEMS PROJECTS OFFICE 1931 JEFFERSON DAVIS HIGHWAY ARLINGTON, VA 20390 ATTN NSP2201, LAUNCHING & HANDLING BRANCH, BR ENGINEER, P. R. FAUROT ATTN NSP-230, FIRE CONTROL & GUIDANCE BRANCH, BR ENGINEER, D. GOLD ATTN NSP-2701, MISSILE BRANCH, BR ENGINEER, J. W. PITSENBERGER	HARRY DIAMOND LABORATORIES ATTN DANIEL, CHARLES D., JR., MG, COMMANDING GENERAL (ERADCOM) ATTN RAMSDEN, JOHN J., LTC, COMMANDER/ FLYER, I.N./LANDIS, P.E./ SOMMER, H./OSWALD, R. B. ATTN CARTER, W.W., DR., TECHNICAL DIRECTOR/MARCUS, S.M. ATTN KIMMEL, S., PAO ATTN CHIEF, 0021 ATTN CHIEF, 0022 ATTN CHIEF, LAB 100 ATTN CHIEF, LAB 200 ATTN CHIEF, LAB 300 ATTN CHIEF, LAB 400 ATTN CHIEF, LAB 500 ATTN CHIEF, LAB 600 ATTN CHIEF, DIV 700 ATTN CHIEF, DIV 800 ATTN CHIEF, LAB 900 ATTN CHIEF, LAB 1000 ATTN RECORD COPY, BR 041 ATTN HDL LIBRARY (5 COPIES)
COMMANDER NAVAL SURFACE WEAPONS CENTER WHITE OAK, MD 20910 ATTN CODE 222, ELECTRONICS & ELECTRO- MAGNETICS DIV ATTN CODE 431, ADVANCED ENGR DIV	
US AIR FORCE, HEADQUARTERS DCS, RESEARCH & DEVELOPMENT WASHINGTON, DC 20330 ATTN DIR OF OPERATIONAL REQUIREMENTS AND DEVELOPMENT PLANS, S/V & LTC P. T. DUESBERRY	

DISTRIBUTION (Cont'd)

HARRY DIAMOND LABORATORIES (Cont'd)
ATTN CHAIRMAN, EDITORIAL COMMITTEE
ATTN CHIEF, 047
ATTN TECH REPORTS, 013
ATTN PATENT LAW BRANCH, 071
ATTN GIDEP OFFICE, 741
ATTN LANHAM, C., 0021
ATTN CHIEF, 0024
ATTN CHIEF, 1010
ATTN CHIEF, 1020 (20 COPIES)
ATTN CHIEF, 1030
ATTN CHIEF, 1040
ATTN CHIEF, 1050
ATTN NOON, T. V., 1020